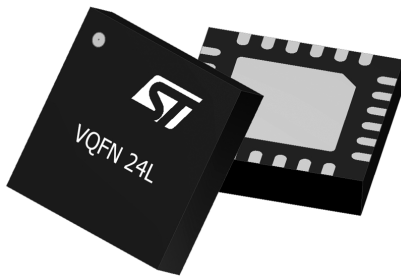


## Power management IC - 2 E-fuses, 2 switching regulators



### Features

- E-fuse 12 V
  - Current limit
  - Current monitor
  - Soft-start with current limit
  - Voltage clamp
  - Dedicated thermal protection
- E-fuse 5 V
  - Current limit
  - Reverse current protection
  - Current monitor
  - Soft-start with current limit
  - Voltage clamp
  - Dedicated thermal protection
- 0.9 V - 3.5 A switching regulator
  - Soft-start
  - Overcurrent
  - Undervoltage monitor
  - 6-bit margining
- 3.3 V - 300 mA switching regulator
  - Soft-start
  - Overcurrent
  - Undervoltage monitor
  - 5-bit margining
- High speed I2C serial interface (3.4 MHz)
- Temperature monitor and shutdown
- Power disable function

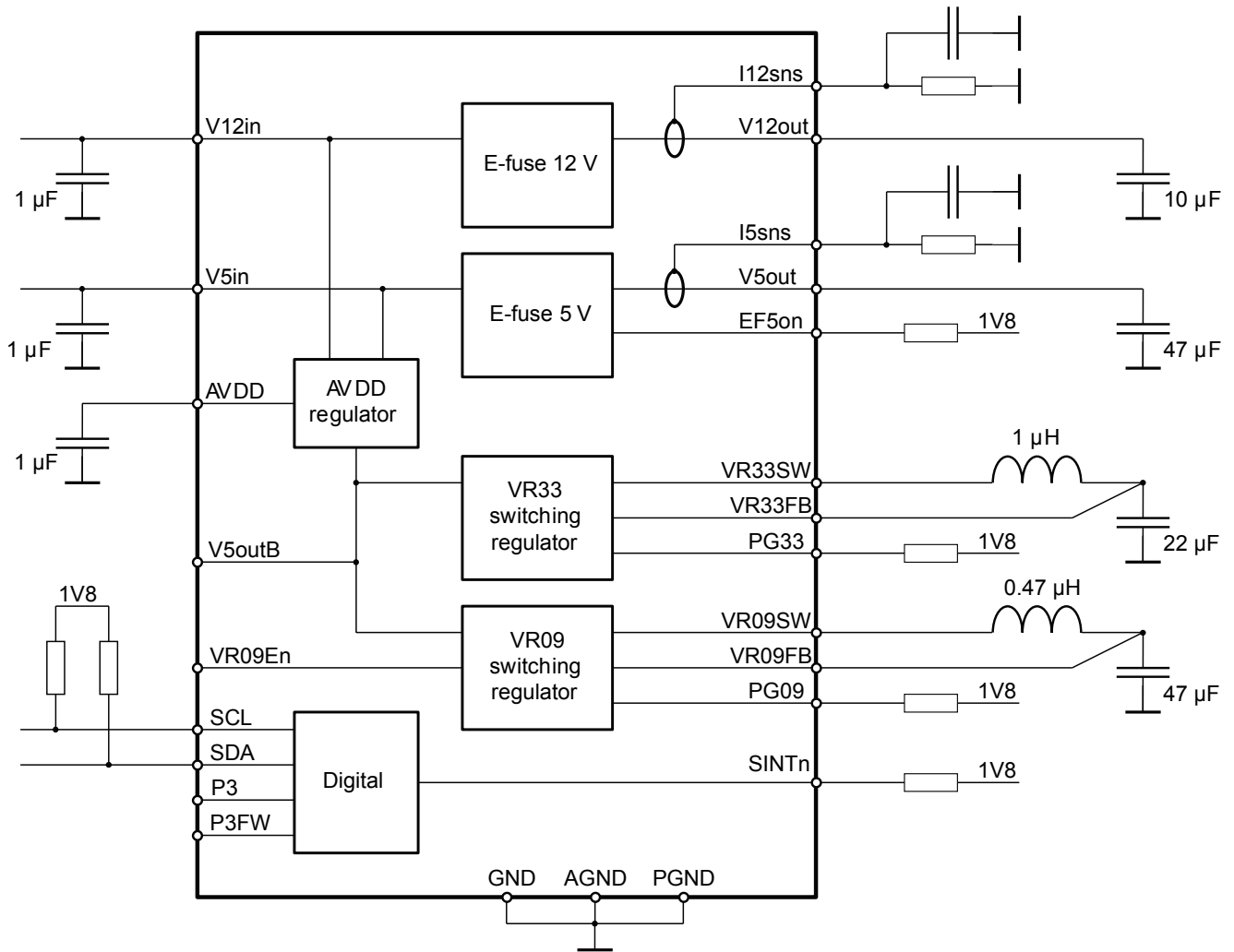
Product status link		
<a href="#">STPMIC02</a>		
Product summary		
Order code	Package	Packing
STPMIC02	VQFN 24-pin with EPAD	Tray
STPMIC02TR	VQFN 24-pin with EPAD	Tape and reel 13"

### Description

The **STPMIC02** chip is a power management device (PMIC) that integrates 2 E-fuses and 2 switching regulators. The chip supports a high speed (3.4 MHz) serial interface with the I2C serial protocol. This interface is bidirectional allowing the microprocessor to set the functions and read status.

# 1 Block diagram

Figure 1. Block diagram



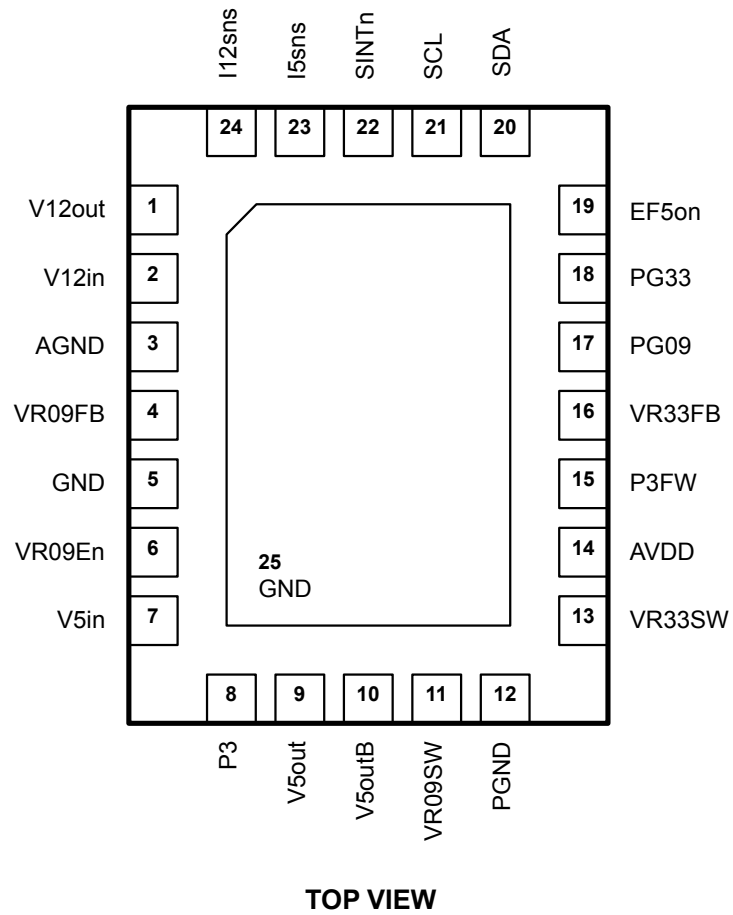
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## 2 Pin description and pinout

**Table 1. Pin description**

Pin no.	Pin name	Description	Direction
1	V12out	12 V output from the E-fuse 12 V	Output power
2	V12in	12 V power supply	Input power
3	AGND	Analog ground	-
4	VR09FB	0.9 V regulator feedback voltage	Input
5	GND	Ground	-
6	VR09En	0.9 V regulator START/STOP command	Input
7	V5in	5 V power supply	Input power
8	P3	Power disable input	Input pull-down
9	V5out	5 V output from the E-fuse 5 V	Output power
10	V5outB	Power supply for 3.3 V and 0.9 V regulators	Input power
11	VR09SW	0.9 V regulator switching node	Output power
12	PGND	Power ground	-
13	VR33SW	3.3 V regulator switching node	Output power
14	AVDD	Internal analog supply	-
15	P3FW	Allow FW to control P3 functions	Input
16	VR33FB	3.3 V regulator feedback voltage	Input
17	PG09	VR 0.9 V Power Good output. Logic0 indicates fault.	Output open drain
18	PG33	VR 3.3 V Power Good output. Logic0 indicates fault.	Output open drain
19	EF5on	E-fuse 5 V state	Output open drain
20	SDA	I <sup>2</sup> C interface data	I/O open drain
21	SCL	I <sup>2</sup> C interface clock	Input
22	SINTn	Interrupt output. Logic0 indicates interrupt.	Output open drain
23	I5sns	E-fuse 5 V current monitor output	Output
24	I12sns	E-fuse 12 V current monitor output	Output

**Figure 2. Pinout**

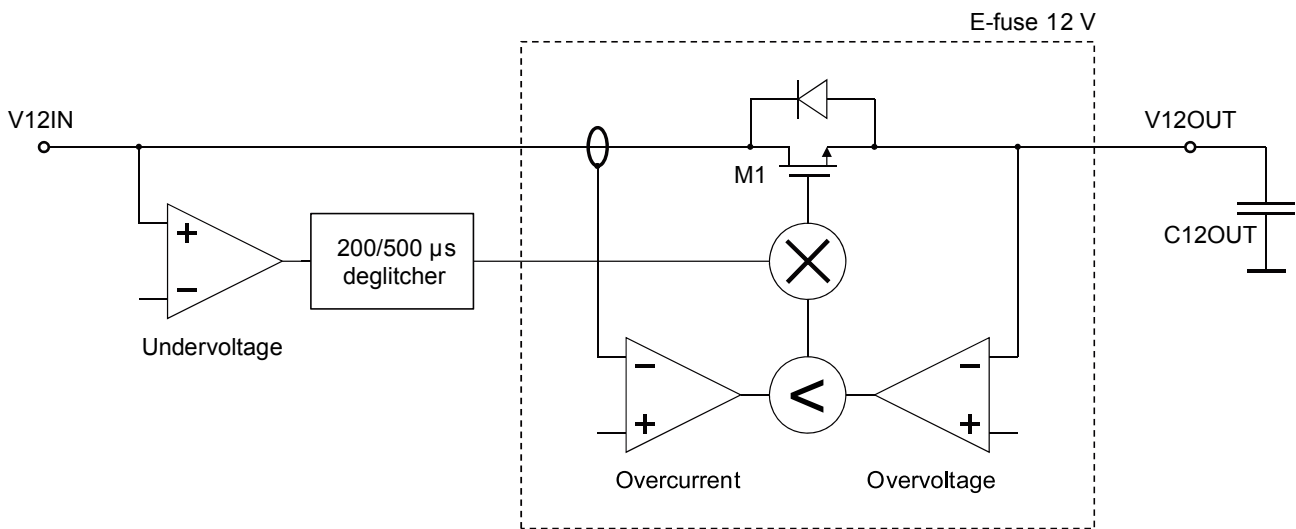


### 3 Functional description

#### 3.1 E-fuse 12 V

The E-fuse 12 V is a high voltage power switch that can limit the voltage or current in extreme conditions of the input overvoltage or output overload current respectively. For this purpose it contains 2 analogue loops, one limiting the output voltage and one limiting the input current as shown in [Figure 3. E-fuse 12 V diagram](#). The current limiting loop is also used during the start-up phase of the E-fuse to limit the inrush current into the V12OUT capacitor.

**Figure 3. E-fuse 12 V diagram**



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In addition, there is a V12IN undervoltage monitor (comparator) to support the E-fuse 12 V subsystem, allowing the E-fuse 12 V to operate only if sufficient V12IN voltage is present. However the signal from the V12IN undervoltage monitor is substantially digitally filtered (deglitcher) before arriving to the E-fuse 12 V in order to prevent unwanted high frequency toggling of the power MOS in case of the noisy V12IN line. If the V12IN falls below the UV12 threshold for longer than 500 µs, the power transistor M1 is turned off, but the intrinsic body diode allows the current to continue flowing back from the V12OUT to V12IN. The E-fuse restarts 200 µs after the V12IN voltage has stabilized above the UV12 threshold.

The E-fuse 12 V can also be manually controlled via the power disable feature of the STPMIC02, which comprises from P3, P3FW and P3En bits as described in [Section 3.7 P3 power disable](#), and is also disabled in case of overtemperature events as described in [Section 3.6 Temperature monitor](#).

The start-up sequence of the E-fuse 12 V is as follows:

- The supply source connected to the V12IN and voltage on the V12IN is higher than the undervoltage threshold.
- If the STPMIC02 is already powered from another power input (V5IN or V5OUTB), the biasing circuitry of the E-fuse 12 V gets enabled, otherwise the STPMIC02 internal start-up sequence would take place (AVDD to reach 1.8 V, see [Section 3.5 AVDD internal supply](#)).
- 100 µs after the biasing enabled, the E-fuse 12 V starts ramping up the V12OUT voltage.
- Since the voltage on the V12OUT is initially zero (or substantially lower than V12IN), the inrush current starts flowing into the V12OUT capacitor limited by the current loop to 0.8 A (typ.).
- When the V12OUT reaches the V12IN, the inrush current disappears, which is an indication that the start-up phase is over.

- The E-fuse 12 V increases the current limit to 3.5 A.

The start-up current limitation loop forces the OC12 flag in the Status1 register high and as a result the SINTn stays low during the start-up even if the rest of the flags are cleared. Software can detect the end of the start-up phase by continuously reading and writing the Status1 register via I<sup>2</sup>C and checking for the OC12 flag presence.

If the V12IN continues rising above the overvoltage threshold (Voclamp), the E-fuse 12 V will limit the output voltage to the Voclamp limit. The E-fuse 12 V will operate in this state until it hits its overtemperature (OT12) threshold and shuts down. Anytime the E-fuse is shutdown due to crossing the OT12 threshold, it would not restart automatically. The E-fuse 12 V can be restarted manually by toggling the P3 pin or performing a power-up cycle on the V12IN or V5IN as soon as the temperature drops by at least the OT hysteresis window.

### 3.1.1 E-fuse 12 V current limit

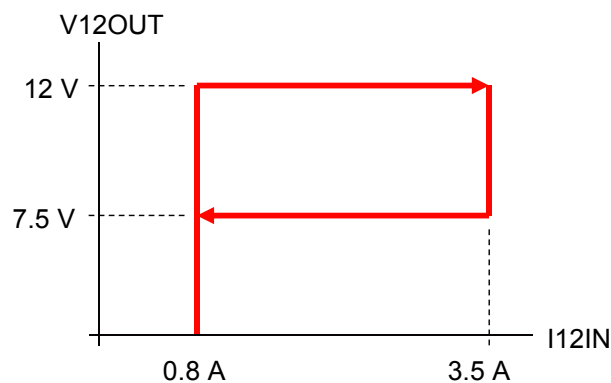
The E-fuse 12 V has 3 kinds of current limit protection mechanisms:

- Start-up current limit of 0.8 A (typ.), activated every time after enable.
- Operative current limit of 3.5 A (typ.), activated when the V12OUT reaches the V12IN .
- Short-circuit protection current limit of 0.8 A (typ.) that is applied when the V12OUT drops below 7.5 V (1.5 V below the undervoltage threshold).

Once the current limit is reduced from 3.5 to 0.8 A due to V12OUT dropping below 7.5 V, the start-up and short-circuit current limits remain activated until the V12OUT reaches its final value.

If the operation of the E-fuse 12 V has been interrupted for any reason (long enough V12IN glitch, thermal event, P3), the E-fuse 12 V restarts with the start-up current limit of 0.8 A regardless of the actual V12OUT output voltage.

**Figure 4. E-fuse 12 V current limit**

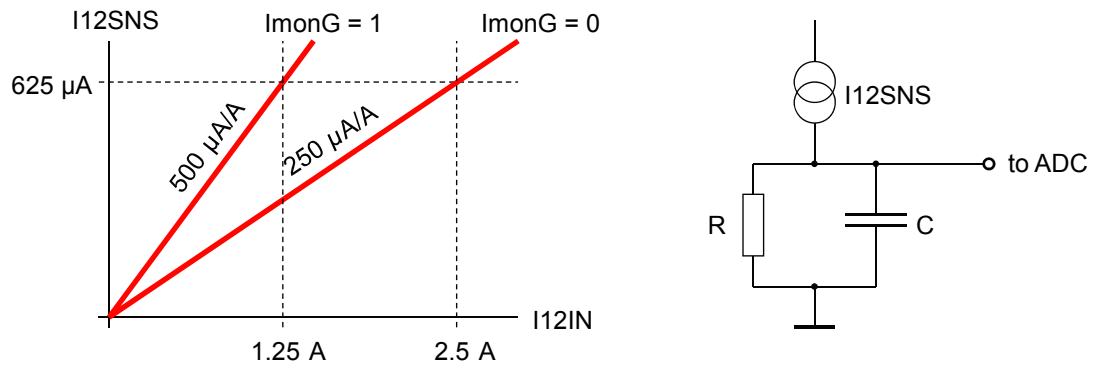


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### 3.1.2 E-fuse 12 V current monitor

The E-fuse 12 V is equipped with a current monitoring capability that allows the host processor to read the current flowing through the E-fuse 12 V. The Imon has two different gain selections to allow for better resolution of the current at different ranges. An external RC filter is used to convert the sensing current into voltage for further processing by the ADC of the host processor.

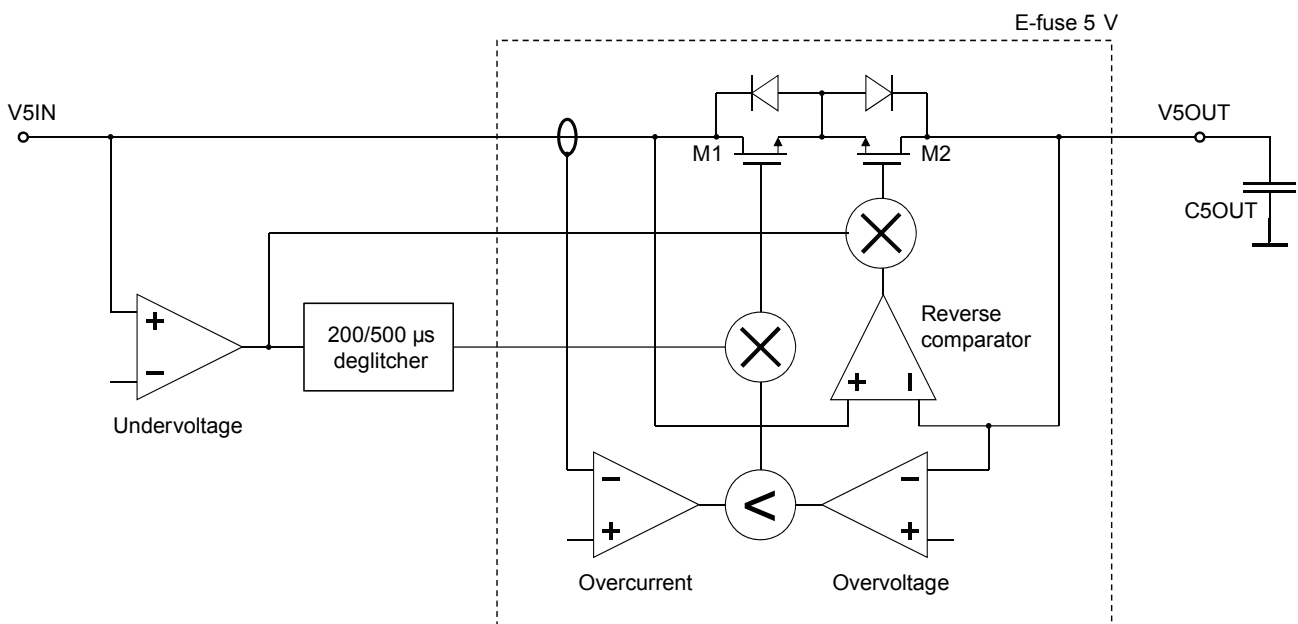
By default (at start-up) the current monitor is off, but can be turned on by writing into the CONTROL0 register. Note that the control bits are common for both E-fuse 12 V and E-fuse 5 V.

**Figure 5. E-fuse 12 V current monitor transfer function**


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### 3.2 E-fuse 5 V

The E-fuse 5 V is a power switch with voltage and current limitation features very similar to the E-fuse 12 V. In addition, the E-fuse 5 V contains a second power transistor M2 (ISOFET) that is able to prevent the significant current flowing back from the V5OUT into the V5IN in case of the V5IN short to ground (or similar such as a deep V5IN glitch). To control the M2, there is also a reverse comparator continuously monitoring the difference between the V5IN and V5OUT.

**Figure 6. E-fuse 5 V diagram**


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As soon as the reverse comparator detects significant negative voltage across the E-fuse 5 V (typically 40 mV), the M2 is turned off immediately. The M2 can be turned back on again only if the voltage across the E-fuse 5 V has become zero (no negative current). However, in case of slow V5IN decay, the V5OUT voltage follows the V5IN because the V5OUT capacitor is being discharged through the E-fuse 5 V into the V5IN and hence no significant negative voltage is generated across the E-fuse 5 V. In that case the V5IN undervoltage monitor serves as a “stop loss” feature, meaning the information from the reverse comparator is overridden by the V5IN undervoltage monitor and the M2 is forced to turn off.

It should be noted that when V5IN undervoltage is detected, the M2 is turned off immediately (asynchronously), however the M1 is kept turned on for next 500  $\mu$ s due to the digital filter (deglitcher) present between the V5IN undervoltage monitor and the E-fuse 5 V. If the V5IN is recovered within the deglitch time of the V5IN undervoltage monitor, the

E-fuse 5 V is able to rapidly restore its normal operating state (warm restart). For longer than the 500  $\mu$ s V5IN glitch, the E-fuse 5 V will shut down completely. The E-fuse 5 V restarts 200  $\mu$ s after the V5IN voltage has stabilized above the UV5 threshold with a regular start-up sequence (cold start) equivalent to start-up sequence of the E-fuse 12 V.

The E-fuse 5 V has the same manual power disable features using P3, P3FW and P3En bits (section 4.7) and equivalent thermal protection mechanism (Section 3.6 Temperature monitor) as the E-fuse 12 V.

### 3.2.1 E-fuse 5 V current limit

The E-fuse 5 V has 3 kinds of current limit protection mechanisms:

- Start-up current limit of 0.8 A (typ), activated every time after enable.
- Operative current limit of 3.5 A (typ), activated when V5OUT reaches V5IN .
- Short-circuit protection current limit of 0.8 A (typ) that is applied when V5OUT drops below 2.5 V (minimum operating voltage of VR09 and VR33 regulators).

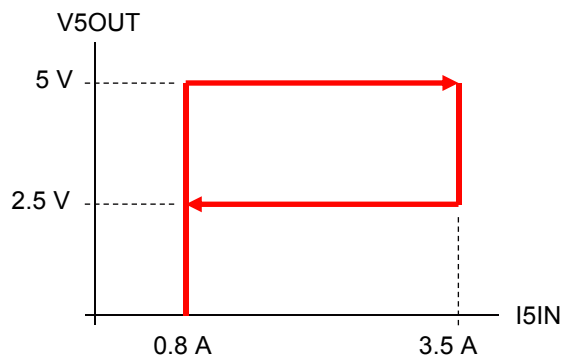
Once the current limit is reduced from 3.5 to 0.8 A due to V5OUT dropping below 2.5 V, the start-up and short-circuit current limits remain activated until the V5OUT reaches its final value.

If the operation of the E-fuse 5 V has been interrupted for any reason (long enough V5IN glitch, thermal event, P3), the E-fuse 5 V restarts with:

- Start-up current limit of 0.8 A, if V5OUT < 2.5 V.
- Operative current limit of 3.5 A, if V5OUT > 2.5 V .

The behaviour of the E-fuse 5 V is different from the E-fuse 12 V in this respect.

Figure 7. E-fuse 5 V current limit



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### 3.2.2 E-fuse 5 V current monitor

The E-fuse 5 V current monitor is identical to the E-fuse 12 V current monitor (see Section 3.1.2 E-fuse 12 V current monitor).

### 3.2.3 EF5ON function

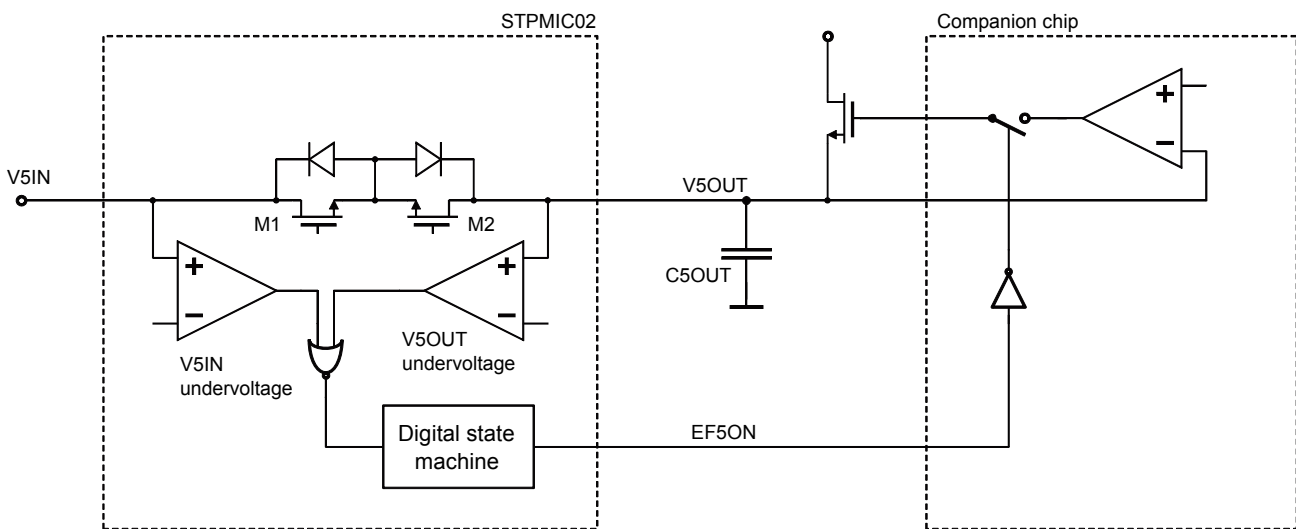
The EF5ON is an output digital signal (open drain) that informs the external world (a companion chip) about the STPMIC02 inability to maintain power-on the V5OUT. As such, the timing of the EF5ON is very critical to prevent the V5OUT power loss. Figure 8. STPMIC02 and external companion device configuration shows the intended usage of the EF5ON signal in a real application.

The function of the EF5ON is shown in Table 2. EF5ON pin - function:



**Table 2. EF5ON pin - function**

EF5ON	Status
0	STPMIC02 cannot guarantee supplying V5OUT node
Hi-Z	STPMIC02 is supplying V5OUT node at nominal operating voltage

**Figure 8. STPMIC02 and external companion device configuration**


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From the timing perspective, it is the rising and falling edge occurrence that is important in maintaining the V5OUT voltage alive. The falling edge on the EF5ON occurs anytime the STPMIC02 detects that it cannot maintain the voltage on the V5OUT, specifically when:

- $(V5IN < \text{threshold})$  and  $(V5OUT < \text{threshold})$ .
- Thermal event on the E-fuse 5 V.
- The STPMIC02 is disabled via P3 power disable control (see section [Section 3.7 P3 power disable](#)).

The first condition above is the most important one in the normal operation as it provides means of filtering V5IN power glitches. In case of a short power glitch on the V5IN, the reverse comparator of the E-fuse 5 V switches off the isolation transistor M2 as described above. At that moment the STPMIC02 is not delivering power to the V5OUT node and only the V5OUT capacitor is powering the systems connected to the V5OUT. As a result the V5OUT voltage starts dropping at a rate proportional to the load current and inversely proportional to the size of the V5OUT capacitor. As soon as the V5OUT drops below 4.4 V (detected by a dedicated comparator on the V5OUT), the EF5ON is reset to logic zero asynchronously.

It should be noted that the EF5ON is not reset when the V5OUT is below a threshold of 4.4 V but the V5IN is in the normal operating range (above UV5V threshold). Similarly, when the V5IN is lost but for any reason the V5OUT is held in the normal operating range, the EF5ON is not reset immediately (for the initial 200  $\mu\text{s}$ ). Such situations do not indicate loss of power on the V5OUT. However the EF5ON defaults to logic 0 if the V5IN is lost for more than 200  $\mu\text{s}$  irrespective of the state of the V5OUT.

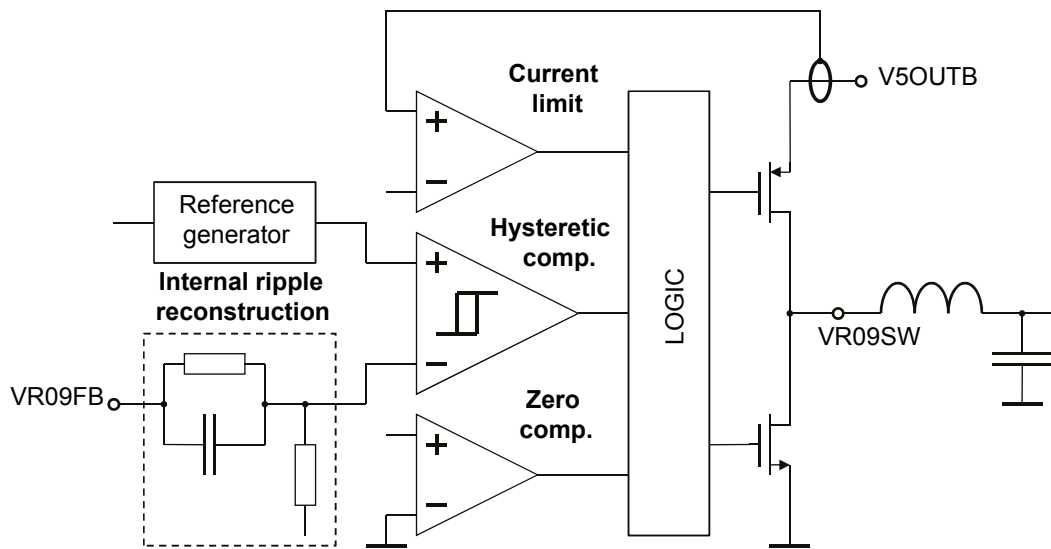
A rising edge on the EF5ON occurs when the STPMIC02 detects that the E-fuse 5 V is providing stable power to the V5OUT node. Meaning that during a short V5IN glitch, the V5OUT typically drops by certain voltage. To recover this drop on the V5OUT, the E-fuse 5 V may or may not reach the current limit of 3.5 A depending on the severity of the event.

A digital counter counts 200  $\mu\text{s}$  after the last occurrence of the E-fuse 5 V overcurrent, then it sets the EF5ON to logic one.

### 3.3 VR09

The VR09 is a fully integrated switching regulator. This regulator features adjustable output voltage with the power monitor, overcurrent protection and low power mode. The power stage is a synchronous rectifier built around two complementary power MOSs of the P-type for the high-side transistor and N-type of the low-side. The control of this power stage is performed by a hysteretic controller. The power stage together with the controller are depicted in [Figure 9. 0.9 V regulator block diagram](#).

**Figure 9. 0.9 V regulator block diagram**



The regulator ON/OFF control is based on input pins VR09En, V5outB and the register VR09Dis as shown in [Table 3. 0V9 regulator ON/ OFF control setting](#).

**Table 3. 0V9 regulator ON/ OFF control setting**

V5outB	VR09En (pin)	VR09Dis (bit)	VR09 state	Comment
Undervoltage	X	X	OFF	Undervoltage on V5outB
OK	0	0 <sup>(1)</sup>	OFF	VR09 disabled by pin (HW)
OK	1	0	ON	-
OK	1	1	OFF	VR09 disabled by FW

1. The VR09Dis bit is automatically reset if the VR09En is LOW.

Whenever the output is 10% below the programmed target output voltage, the PG is triggered and the bit UV09 is set along with the PG09 pin pulled low to indicate a fault.

The regulator VR09 will be also switched off if the internal temperature sensor reaches the overtemperature (OT) level. It's restarted automatically once the die temperature drops below the OT threshold (see also [Section 3.6 Temperature monitor](#)).

#### 3.3.1 VR09 low power mode

The VR09 features a low power mode which prevents degradation of the efficiency for the light-load. In case of the light-load, the current in the coil could reverse (flow from the output to the ground through low-side power MOS). This behaviour is causing strong degradation of the efficiency of the regulator. In order to prevent such degradation, the VR09 features

a low power mode. When the current reverses in the coil, this is detected by a so-called “zero-comparator” and the conduction of the low-side NMOS is stopped. The power stage is then maintained in high impedance until the output voltage falls below the reference  $V_{ref\_VR09}$  where a new pulse is initiated with the following scheme:

- Conduction of the high-side MOS.
- Conduction of the low-side MOS.
- Depending whether the hysteretic comparator or zero-comparator triggers first:
  1. If the zero-comparator is first, the power stage is kept in high impedance until the hysteretic comparator triggers, in which case the step one is initiated.
  2. In case it is the hysteretic comparator, the controller initiates a new cycle at the step one without transition of the power stage in high impedance state.

In the low power mode, it is the pulse occurrence frequency which is modulated as

a function of the load current as the regulator is operating in the pulse frequency modulation (PFM) mode. Entering and leaving the PFM mode is performed automatically and the transition is transparent to the user.

The operation in the low power mode can be inhibited by setting the bit 4 in the register CONTROL0.

### 3.3.2 VR09 current limit

The input current of the VR09 regulator is monitored by a current limit comparator. Shall the input current exceeds the limit value  $I_{peak\_max\_vr09}$ , the conduction of the high-side MOS is disabled and low-side MOS conduction is forced for a given time: the overcurrent  $T_{off}$  time. Such event also leads the bit OC09 in the register STATUS1 to be set. After the timing elapsed, the state of the power stage is set according to the output of the hysteretic comparator.

If both overcurrent and undervoltage conditions are detected, the regulator is forced off for the duration in the order of 4 ms. It is restarted after this duration.

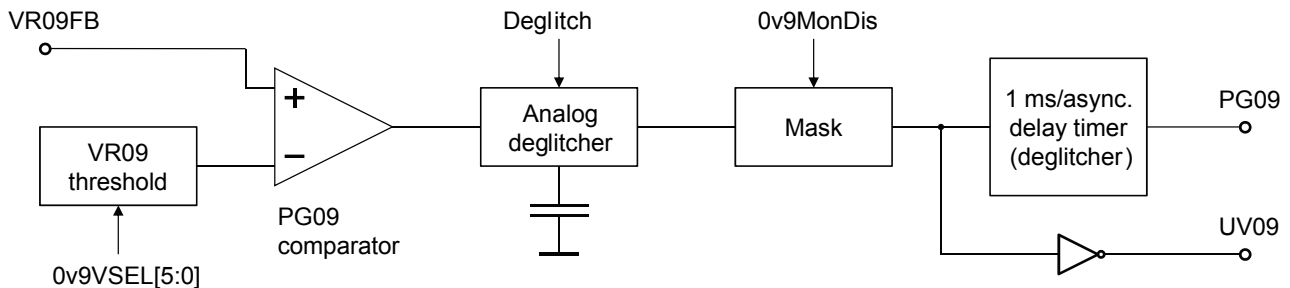
### 3.3.3 FW enable/disable: VR09Dis, VR09MonDis and VR09Key bits

The behaviour is as follows:

- If the pin VR09En = 0, the bits VR09Dis and VR09MonDis will be reset (to value 0).
- If the pin VR09En = 1, the bits VR09Dis and VR09MonDis may be modified by following sequence of I<sup>2</sup>C accesses:
  1. Set the bit 5 at the register 3V3 VSEL to set the VR09Key bit to 1
  2. Write at the CONTROL0 register - bits VR09Dis and VR09MonDis will be modified.
- The register VR09Key remains set only for one consecutive I<sup>2</sup>C write operation and afterwards it's reset to 0 again. Thus any intermediate I<sup>2</sup>C write operation between steps 1. and 2. will cause that the step 2. will not overwrite the bits VR09Dis and VR09MonDis.
- The 0V9 regulator will be enabled when VR09En = 1 and VR09Dis = 0. Any other combination of the pin and register will disable the 0V9 regulator.
- The bit VR09MonDis causes voltage monitoring disable. See [Section 3.3.5 VR09 software control sequence](#) describing effect of the VR09MonDis on the PG09 output pin.
- The bit VR09MonDis is intended to be set by I<sup>2</sup>C and reset internally by the STPMIC02. The register is reset every time the VR09 performs a transition (start-up sequence or change of output voltage based on 0V9Sel register change).

### 3.3.4 Power monitor functions

The power monitor function of the VR09 monitors the regulator output (VR09FB) and drives the PG09 pin low when VR09FB output voltage is 10% below the targeted voltage setting. There is no voltage hysteresis on the VR09 monitor, only asymmetric timing deglitcher. As soon as the VR09FB voltage drops below the threshold, the power monitor will drive the PG pin to the Logic0 immediately (asynchronously). Contrary, when the VR09FB voltage has recovered, a 1 ms one-shot delay timer is triggered and upon timer timeout, the PG is allowed to go to the Logic1 state.

**Figure 10. 0.9 V regulator power monitor block diagram**


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The PG09 output has the following logic:

- If the VR09 is switched OFF, the PG09 is LOW.
- If the VR09 is ON but the PG09MonDis is asserted (1) in [Figure 11. 0.9 V regulator control sequence](#), the PG09 holds its last value.
- If the VR09 is ON and PG09MonDis = 0 then:
  1. During any transition (voltage change) the PG09 holds its last value before transition (during the initial start-up the PG09 is LOW) until the output voltage reaches the new target value.
  2. During the steady state (no transition in progress), the PG09 drops when undervoltage at the VR09 output is indicated and rises if the voltage is valid for at least 1 ms consecutively. Spikes of the detector are filtered according to bit deglitch as defined in the register CONTROL0 (see [Section 4.6 CONTROL0 address = 4 \(0x04h\)](#)).

### 3.3.5 VR09 software control sequence

This paragraph describes a sequence to disable the VR09 by the I<sup>2</sup>C register and restart it.

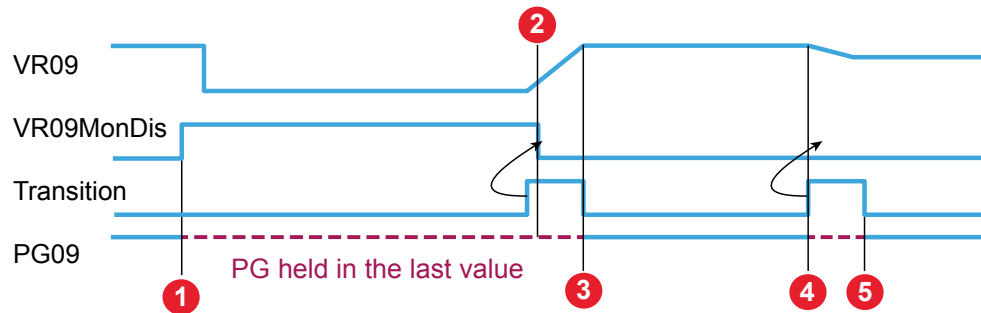
VR09 disable:

- Set the bit 5 at the register 3V3 VSEL to set the VR09Key bit to 1.
- Set the bit 1 at the register CONTROL0 to set the bit VR09MonDis.
- Set again the bit 5 at the register 3V3 VSEL to set the VR09Key bit to 1.
- Set the bit 0 at the register CONTROL0 (keeping also bit 1 at value 1) to set the bit VR09Dis.

VR09 restart:

- Set the bit 5 at the register 3V3 VSEL to set the VR09Key bit to 1.
- Reset the bit 0 at the register CONTROL0 to reset the bit VR09Dis.

*Note:* The bit VR09MonDis will be auto-reset during the VR09 ramp-up to ensure stable value of the PG09 (see also [Section 3.3.3 FW enable/disable: VR09Dis, VR09MonDis and VR09Key bits](#) and [Section 3.3.4 Power monitor functions](#)).

**Figure 11. 0.9 V regulator control sequence**


Between the point (1) and (2), the PG09 is held in the last value due to the VR09MonDis being set. The bit VR09MonDis is reset at the point (2) but the PG09 is still held due to transition in progress. As a side effect, the VR09MonDis would be also reset between points (4) and (5) due to VR09 transition.

### 3.4 VR33

The VR33 is a fully integrated switching regulator. This regulator features adjustable output voltage with the power monitor, overcurrent protection and low power mode similarly as the VR09. Whenever the output is 10% below the programmed target output voltage, the PG is triggered and the UV33 bit is set along with the PG33 pin pulled low to indicate a failure.

This regulator starts when the V5OUTB is crossing the start regulator threshold. It will stop when the V5OUTB is below its min. supply for a proper operation. The start/stop thresholds are different.

#### 3.4.1 VR33 low power mode

The operation of the low power mode for the VR33 regulator is exactly the same as for the VR09. The VR33 low power mode operation can be inhibited by setting the bit 5 in the register CONTROL0.

#### 3.4.2 VR33 current limit

The operation of the VR33 current limit is similar as the one of the VR09. In case the VR33 current exceeds  $I_{peak\_max\_vr33}$ , the bit OC33 in the register STATUS1 is set.

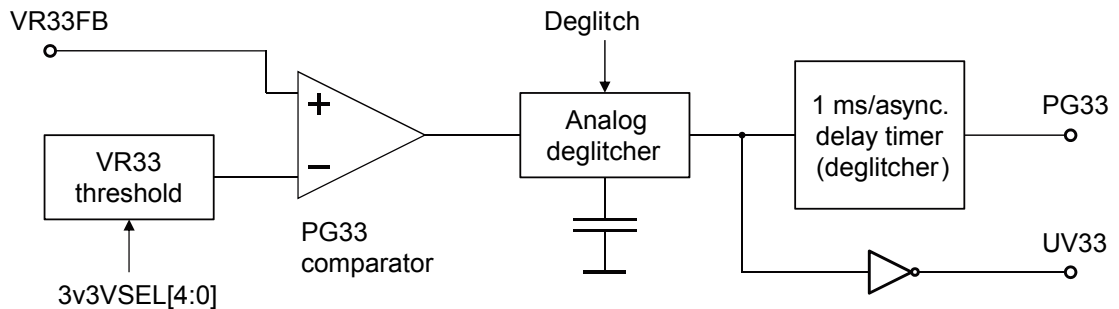
#### 3.4.3 VR33 full duty operation

In case the input voltage is not high enough (too low difference input voltage, output voltage) to maintain the normal periodic operation, the VR33 regulator will modulate the frequency at which low-side MOS pulses are issued. Ultimately if the input voltage is not sufficient to meet the target output voltage, the high-side MOS is kept on continuously. Thanks to the hysteretic regulation, this behaviour is natively supported by the controller with no undershoot or overshoot when entering or leaving the full duty operation.

#### 3.4.4 Power monitor functions

Power monitoring circuitry of the VR33 is equivalent to the VR09 monitor except there is no monitor disable functionality.

Figure 12. 3.3 V regulator power monitor block diagram



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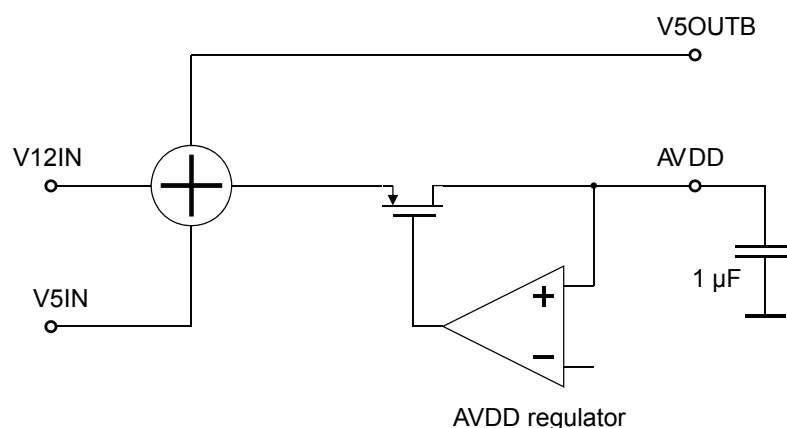
The PG33 output has the following logic:

- If the VR33 is switched OFF, the PG33 is LOW.
- If the VR33 is ON then:
  1. During any transition (voltage change) the PG33 holds its last value before transition (during the initial start-up the PG33 is LOW) until the output voltage reaches the new target value.
  2. During the steady state (no transition in progress), the PG33 drops when undervoltage at the VR33 output is indicated and rises if the voltage is valid for at least 1 ms consecutively. Spikes of the detector are filtered according to the bit deglitch as defined in the register CONTROL0 (see [Section 4.6 CONTROL0 address = 4 \(0x04h\)](#)).

### 3.5 AVDD internal supply

The STPMIC02 chip can be powered from either V5IN or V12IN or V5OUTB, depending on presence of power-on the 3 respective inputs. The STPMIC02 automatically chooses the input where power is present and operates from that input autonomously. This is true for both start-up conditions as well as the normal run-time operation, i.e.: the STPMIC02 can dynamically change the source of its power when running. However, the V5OUTB is the preferred source of power for the STPMIC02 over the V5IN and V12IN, while V5IN and V12IN are having equal weight should power be present on more than one input.

Figure 13. AVDD internal supply block diagram



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The internal power supply of the STPMIC02 is totally independent from the E-fuse 5 V and E-fuse 12 V operation as well as the E-fuse 5 V and E-fuse 12 V can be turned on / turned off independently from each other.

Since the AVDD regulator contains a current limitation feature designed to cover the quiescent consumption needs of the STPMIC02 itself, it is prohibited to connect any additional static current consumption to the AVDD pin.

### 3.6 Temperature monitor

The chip has three on die temperature sensors for thermal protection as well as system warning of impending overtemperature. Upon hitting the EOTW threshold, the chip will set the EOTW bit and pull the SINTn pin low to alert the processor. If the temperature continues to rise above the OT threshold, the chip will shut the E-fuse or VR that causes the OT off to allow for cool down.

There are 3 status bits for thermal warning (one bit from each sensor) but only 2 bits for overtemperature (shutdown) in the register map. When the first sensor reaches the OT threshold, this state is latched and the sensor is identified by binary value according to [Table 4. Overtemperature shutdown](#):

**Table 4. Overtemperature shutdown**

OT<1:0>		Overtemperature sensor
OT12	OT5	
0	0	No overtemperature detected
0	1	1 <sup>st</sup> sensor (E-fuse 5) tripped overtemperature
1	0	2 <sup>nd</sup> sensor (E-fuse 12) tripped overtemperature
1	1	3 <sup>rd</sup> sensor (VR09) tripped overtemperature

If more sensors reach the OT threshold, the status remains unchanged until the first sensor drops below the falling OT threshold. If there's still some other sensor in the OT region the indication will change to that one.

### 3.7 P3 power disable

The chip has a HW programmable feature for the P3 power disable. When the P3FW pin is at the Logic0, the P3 pin has direct control of the E-fuses to control the turn on/off power to the rest of the electronics. When the P3FW pin is at the Logic1, FW is allowed to enable/disable the P3 control of the E-fuse.

**Table 5. P3 power disable setting**

VxIN	P3 (pin)	P3FW (pin)	P3En (bit)	E-fuse state	Comment
Undervoltage	X	X	X	OFF	Undervoltage on E-fuse input
OK	0	X	X	ON	P3 = 0, E-fuse always enabled
OK	1	0	X	OFF	P3 = 1, FW control disabled
OK	1	1	0	ON	P3 = 1, E-fuse enabled by FW control
OK	1	1	1	OFF	P3 = 1, E-fuse disabled by FW control

*Note: The truth table above doesn't cover all the factors contributing to E-fuse control (e.g.: reverse condition, thermal shutdown).*

The register bit P3En is reset by undervoltage on any E-fuse input (i.e. V5IN or V12IN). In the situation when P3 = 1, P3FW = 1 and software disabled E-fuses by writing the P3En bit = '1', a pulse on the VxIN input will reset the P3En bit which leads to restart of E-fuses.

### 3.8 SINTn function

The SINTn pin will set to the Logic0 whenever any on the fault is set in the fault registers. This includes the change of the state for the P3 pin. Whenever a fault status bit is set, the SINTn output is Logic0 until all the fault sources have disappeared and affected status bits are cleared by FW by writing to the status register.

### 3.9 I<sup>2</sup>C serial interface

The chip supports a high speed serial interface with the I<sup>2</sup>C serial protocol. This interface is bidirectional allowing the microprocessor to set up functions and read status. The I<sup>2</sup>C interface is standard implementation with the speed of the fast speed I<sup>2</sup>C up to the 3.4 MHz operation. The interface voltage is 1.8 V with the CMOS level interfacing as required by the I<sup>2</sup>C standard.

#### 3.9.1 Slave address

The I<sup>2</sup>C address of the device is 0x33h (51 decimal) in a 7-bit format. This 7 bits long address is followed by an eight bit which is a data direction bit R/W. A '0' indicates a transmission 'write', a '1' indicates a request for data 'read'.

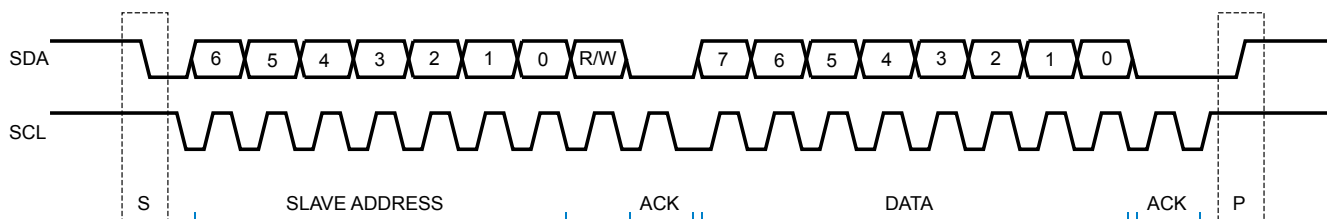
Table 6. I<sup>2</sup>C address

7	6	5	4	3	2	1	0
Slave address							Dir
0	1	1	0	0	1	1	R/W

#### 3.9.2 I<sup>2</sup>C functional operation

The I<sup>2</sup>C embedded in the STPMIC02 behaves like a slave device and the data transfers follow the format shown in Figure 14. Data transfer on the I<sup>2</sup>C bus.

Figure 14. Data transfer on the I<sup>2</sup>C bus



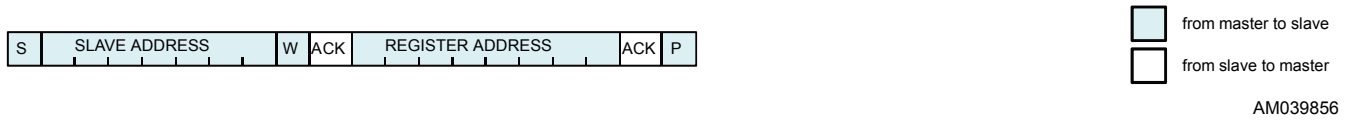
Within the procedure of the I<sup>2</sup>C bus, unique situations arise which are defined as START and STOP conditions. A 'high' to 'low' transition is on the SDA line while SCL is 'high' is one such unique case. This situation indicates the START condition (S). A 'low' to 'high' transition on the SDA line while SCL is 'high' defines the STOP condition (P). START and STOP conditions are always generated by the master. The bus is considered to be busy after the START condition. The bus is considered to be free again a certain time after the STOP condition.

After the START condition, a 7-bit long slave address is sent by the master followed by the R/W bit as described in Section 3.9.1 Slave address. The data transfer should be acknowledged by the receiver, i.e. by the slave in case of transmitting the slave address. The acknowledge related clock pulse (ACK) is generated by the master. The transmitter releases the SDA line ('high') during the acknowledge clock pulse. The receiver should pull down the SDA line during the acknowledge clock pulse so that it remains stable 'low' during the 'high' period of this clock pulse. When a slave receiver does not acknowledge the slave address, the data line must be left 'high' by the slave. The master can then generate a STOP condition to abort the transfer.

After the slave address has been sent by the master and acknowledged by the slave, the following byte contains the STPMIC02 register address to be accessed. The valid register address range is 0x00h to 0x06h and 0x10h to 0x11h. The full address space is described in Section 4 Register description and defaults. It is assumed that the first I<sup>2</sup>C register access after POR will be reading operation from the register address 0x00h in order to identify the device by the master.

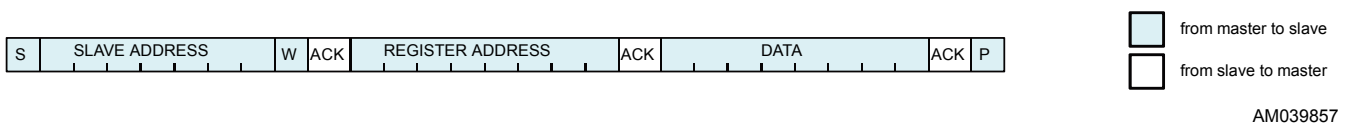


Figure 15. Setting register address operation



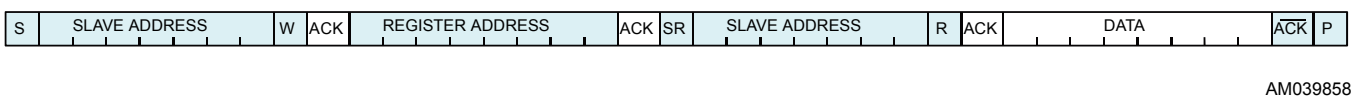
In case of a write cycle to a STPMIC02 register, the third byte is the actual data to be written to the register address specified in the second byte. A complete single byte write cycle would look like in [Figure 16. Single data byte write operation](#):

Figure 16. Single data byte write operation



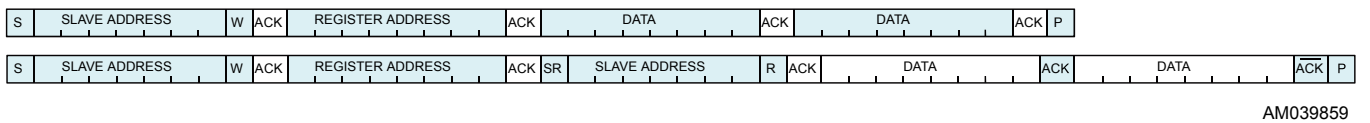
However, if a master wishes to read data from the STPMIC02, it can generate a repeated START condition (SR) without first generating a STOP condition. In this case the slave address is transmitted twice, once for the register address write and once for the data read operation. The read transaction is ended by the master not acknowledging the data byte and generating the STOP condition.

Figure 17. Single data byte read operation



The STPMIC02 also supports multiple data read / write operations, automatically incrementing the register address after each data byte access. The multiple data write and multiple data read operations are shown in [Figure 18. Multiple data bytes write/read operation](#).

Figure 18. Multiple data bytes write/read operation



## 4 Register description and defaults

### 4.1 Serial port mapping

**Table 7. Serial port mapping**

Register name	Addr. (dec.)	7	6	5	4	3	2	1	0
ID1	0	DEV1	DEV0	MID2	MID1	MID0	NID2	NID1	NID0
ID2	1	VID3	VID2	VID1	VID 0	FAB1	FAB0	Reserved <1:0>	
0V9VSEL	2	-	-	0V9Sel5	0V9Sel4	0V9Sel3	0V9Sel2	0V9Sel1	0V9Sel0
3V3VSEL	3	-	-	0V9Key	3V3Sel4	3V3Sel3	3V3Sel2	3V3Sel1	3V3Sel0
CONTROL0	4	P3En	ImonG	VR33PWM	VR09PWM	Deglitch	iMonEn	VR09 MonDis	VR09Dis
STATUS0	5	UV12	UV5	UV33	UV09	OT <1:0>		EOTW12	EOTW5
STATUS1	6	OC12	OC5	OC33	OC09	P3state	EOTW09	Reserved 1	Reserved 0
DeGlitch1	16	EFOV deglitch				Reserved			
DeGlitch2	17	-	-	-	-	EFOC deglitch			

### 4.2 ID1 address = 0 (0x00h)

**Table 8. Die ID1 register**

7	6	5	4	3	2	1	0
DEV		MID			NID		
R		R			R		
0	1	-	-	-	-	-	-

**Table 9. Die ID1 bit description**

Bit no.	Bit name	Description	Meanings	
7:6	DEV<1:0>	Device	01	STPMIC02
5:3	MID<2:0>	Major ID	001	1.x diffusion release
			010	2.x
			011	3.x
			100	4.x
			101	5.x
			110	6.x
			111	7.x

Bit no.	Bit name	Description	Meanings	
2:0	NID<2:0>	Minor ID	000	x.0 metal release
			001	x.1
			010	x.2
			011	x.3
			100	x.4
			101	x.5
			110	x.6
			111	x.7

### 4.3 ID2 address = 1 (0x01h)

**Table 10. Die ID2 register**

7	6	5	4	3	2	1	0
VID				FAB		SID	
R				R		R	
0	0	0	0	OTP	OTP	1	0

**Table 11. Die ID2 bit description**

Bit no.	Bit name	Description	Meanings	
7:4	VID <3:0>	Variant ID	-	-
3:2	FAB <1:0>	Fab.	00 01 10 11	ST Catania
1:0	Reserved <1:0>	-	-	-

### 4.4 0V9 VSEL address = 2 (0x02h)

**Table 12. 0V9 regulator, voltage selection register**

7	6	5	4	3	2	1	0
-	-	0V9Sel					
R	R	R/W					
0	0	1	0	0	0	1	0

**Table 13. 0V9 regulator, voltage selection bit description**

Bit no.	Bit name	Description	Meanings			
5:0	0V9Sel <5:0>	VR09 output voltage select	000000	0.770 V	100000 <sup>(1)</sup>	0.930 V
			000001	0.775 V	100001	0.935 V
			000010	0.780 V	<b>100010</b>	<b>0.940 V <sup>(1)</sup></b>
			000011	0.785 V	100011	0.945 V
			000100	0.790 V	100100	0.950 V
			000101	0.795 V	100101	0.955 V
			000110	0.800 V	100110	0.960 V
			000111	0.805 V	100111	0.965 V
			001000	0.810 V	101000	0.970 V
			001001	0.815 V	101001	0.975 V
			001010	0.820 V	101010	0.980 V
			001011	0.825 V	101011	0.985 V
			001100	0.830 V	101100	0.990 V
			001101	0.835 V	101101	0.995 V
			001110	0.840 V	101110	1.000 V
			001111	0.845 V	101111	1.005 V
			010000	0.850 V	110000	1.010 V
			010001	0.855 V	110001	1.015 V
			010010	0.860 V	110010	1.020 V
			010011	0.865 V	110011	1.025 V
			010100	0.870 V	110100	1.030 V
			010101	0.875 V	110101	1.035 V
			010110	0.880 V	110110	1.040 V
			010111	0.885 V	110111	1.045 V
			011000	0.890 V	111000	1.050 V
			011001	0.895 V	111001	1.055 V
			011010	0.900 V	111010	1.060 V
			011011	0.905 V	111011	1.065 V
			011100	0.910 V	111100	1.070 V
			011101	0.915 V	111101	1.075 V
			011110	0.920 V	111110	1.080 V
			011111	0.925 V	111111	1.085 V

1. Default.

#### 4.5 3V3 VSEL address = 3 (0x03h)

**Table 14. 3V3 regulator, voltage selection register**

7	6	5	4	3	2	1	0
-	-	0V9Key	3 V3Sel				
R	R	R/W	R/W				
0	0	0	1	0	0	1	1

**Table 15. 3V3 regulator, voltage selection bit description**

Bit no.	Bit name	Description	Meanings			
5	0V9Key	Key to enable 0V9 monitor and regulator disable. The bit is reset internally by STPMIC02 by any consecutive I <sup>2</sup> C write operation.				
4:0	3 V3Sel <4:0>	VR33 output voltage select	00000	2.54 V	10000	3.18 V
			00001	2.58 V	10001	3.22 V
			00010	2.62 V	10010	3.26 V
			00011	2.66 V	<b>10011</b> <sup>(1)</sup>	<b>3.30 V</b> <sup>(1)</sup>
			00100	2.70 V	10100	3.34 V
			00101	2.74 V	10101	3.38 V
			00110	2.78 V	10110	3.42 V
			00111	2.82 V	10111	3.46 V
			01000	2.86 V	11000	3.50 V
			01001	2.90 V	11001	3.54 V
			01010	2.94 V	11010	3.58 V
			01011	2.98 V	11011	3.62 V
			01100	3.02 V	11100	3.66 V
			01101	3.06 V	11101	3.70 V
			01110	3.10 V	11110	3.74 V
			01111	3.14 V	11111	3.78 V

1. Default.

## 4.6 CONTROL0 address = 4 (0x04h)

**Table 16. CONTROL0**

7	6	5	4	3	2	1	0
P3En	ImonG	VR33PWM	VR09PWM	Deglitch	iMonEn	VR09MonDis	VR09Dis
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
0	0	0	0	0	0	0	0

**Table 17. CONTROL0 register, bit description**

Bit no.	Bit name	Description
7	P3En	P3 power disable feature enable. The bit is reset internally by the STPMIC02 when undervoltage occurs on V5IN or V12IN supply voltage.
6	ImonG	Current monitor gain
5	VR33PWM	ForceVR33 to operate in PWM mode only.
4	VR09PWM	ForceVR09 to operate in PWM mode only.
3	Deglitch	Deglitch time selection for fault/POR detection (as specified in <a href="#">Section 7.4 VR09</a> ).
2	iMonEn <sup>(1)</sup>	E-fuse current monitor enable.

Bit no.	Bit name	Description
1	VR09MonDis	VR09 PG monitor disable. The bit can be modified only if the bit 0V9Key has been set in previous write. The bit is reset internally by the STPMIC02 when the VR09 performs transition (startup or output voltage change) or when the input pin VR09En is low.
0	VR09Dis	VR09 regulator disable (OFF). The bit can be modified only if the bit 0V9Key has been set in previous write. The bit is reset internally by the STPMIC02 when the input pin VR09En is low.

1. The *iMonEn* bit can be manually set or reset via I<sup>2</sup>C by the user. The *iMonEn* bit keeps its value during the overcurrent and/or overvoltage of any E-fuse. The *iMonEn* bit is totally independent from any VR.

#### 4.7 STATUS0 address = 5 (0x05h)

**Table 18. STATUS0**

7	6	5	4	3	2	1	0
UV12	UV5	UV33	UV09	OT		EOTW12	EOTW5
R/W	R/W	R/W	R/W	R/W		R/W	R/W

**Table 19. STATUS0 register, bit description**

Bit no.	Bit name	Description	Meanings	
7	UV12	12 V input undervoltage	-	-
6	UV5	5 V input undervoltage	-	-
5	UV33	VR33 output undervoltage	-	-
4	UV09	VR09 output undervoltage	-	-
3:2	OT <1:0>	E-fuse 12 V, E-fuse 5 V and/or VR09 overtemperature	00	Normal temperature
			01	E-fuse 5 V overtemperature
			10	E-fuse 12 V overtemperature
			11	VR09 overtemperature
1	EOTW12	E-fuse 12 V early temperature warning	-	-
0	EOTW5	E-fuse 5 V early temperature warning	-	-

Status register bits are latched. Cleared by write action to the status register.

#### 4.8 STATUS1 address = 6 (0x06h)

**Table 20. STATUS1**

7	6	5	4	3	2	1	0
OC12	OC5	OC33	OC09	P3state	EOTW09	Reserved 1	Reserved 0
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

**Table 21. STATUS1 register, bit description**

Bit no.	Bit name	Description
7	OC12	E-fuse 12 V overcurrent
6	OC5	E-fuse 5 V overcurrent
5	OC33	VR33 output overcurrent
4	OC09	VR09 output overcurrent
3	P3state	Present P3 pin state
2	EOTW09	VR09 early temperature warning
1	Reserved 1	-
0	Reserved 0	-

Status register bits are latched. Cleared by write action to the status register.

#### 4.9 Deglitch1 address = 16 (0x10h)

**Table 22. E-Fuse overvoltage deglitch time register**

7	6	5	4	3	2	1	0
EFOV deglitch				Reserved			
R/W				R/W			
1	0	1	0	0	0	0	0

**Table 23. E-Fuse overvoltage deglitch time register, bit description**

Bit no.	Bit name	Description	Meanings			
7:4	EFOV deglitch <3:0>	E-fuse clamping deglitch time (falling edge only)	0000	5 $\mu$ s	1000	40 $\mu$ s
			0001	6 $\mu$ s	1001	48 $\mu$ s
			0010	7 $\mu$ s	1010	56 $\mu$ s
			0011	8 $\mu$ s	1011	64 $\mu$ s
			0100	9 $\mu$ s	1100	72 $\mu$ s
			0101	10 $\mu$ s	1101	80 $\mu$ s
			0110	11 $\mu$ s	1110	88 $\mu$ s
			0111	12 $\mu$ s	1111	96 $\mu$ s
3:0	Reserved	-	-	-	-	

#### 4.10 Deglitch2 address = 17 (0x11h)

**Table 24. E-Fuse overcurrent deglitch time register**

7	6	5	4	3	2	1	0
-	-	-	-	EFOCdeglitch			
R	R	R	R	R/W			
0	0	0	0	0	0	1	1

**Table 25. E-Fuse overcurrent deglitch time register, bit description**

Bit no.	Bit name	Description	Meanings			
3:0	EFOC deglitch <3:0>	E-fuse overcurrent deglitch time	0000	2 $\mu$ s	1000	16 $\mu$ s
			0001	3 $\mu$ s	1001	24 $\mu$ s
			0010	4 $\mu$ s	1010	32 $\mu$ s
			0011	5 $\mu$ s	1011	40 $\mu$ s
			0100	6 $\mu$ s	1100	48 $\mu$ s
			0101	7 $\mu$ s	1101	56 $\mu$ s
			0110	8 $\mu$ s	1110	64 $\mu$ s
			0111	9 $\mu$ s	1111	72 $\mu$ s



## 5 Absolute maximum ratings

The absolute maximum rating is the maximum stress that can be applied to a device without causing permanent damage. However, extended exposure to maximum ratings may affect long-term device reliability.

**Table 26. Absolute maximum ratings**

Parameter	Limit	Unit
12 V power input voltage (maximum 100 msec.)	-0.3 to 25 (without external diode)	V
5 V power input voltage (maximum 100 msec.)	-0.3 to 15 (without external diode)	V
12 V overcurrent protect	3.5	A
5 V overcurrent protect	3.5	A
V5OUTB, V5OUT	-0.3 V to 7	V
V12OUT	-0.3 V to 16.5	V
Operating junction temperature	-10 to 150	°C
P3 input voltage	-0.5 to 3.9	V
P3FW input voltage	-0.5 to AVDD	V
AVDD	-0.5 to 2.5	V
SDA, SCL - I <sup>2</sup> C lines	-0.3 V to 2.5	V
I5SNS, I12SNS	-0.3 V to 7	V
PG09, PG33, EF5ON, VR09En, SINTn	-0.3 V to 7	V
VR33FB	-0.3 V to 5.7	V
VR09FB	-0.3 V to 2.5	V
VR09SW, VR33SW	-0.3 V to 7	V
Thermal resistance, junction to ambient natural convection <sup>(1)</sup>	50	°C/W
Thermal resistance, junction to top case <sup>(2)</sup>	38	°C/W

1. As per std Jedec spec JESD51-7, it could be improved with optimized PCB layout

2. As per std Jedec spec JESD51-12.01, it could be improved with optimized PCB layout.

## 6 Typical operating conditions

Unless otherwise indicated, performance specifications do not apply when the device is operated outside the recommended conditions.

**Table 27. Typical operating conditions**

Parameter	Min.	Typ.	Max.	Unit
12 V power input voltage	10.5	12	13.2	V
12 V power input current	-	-	2.5	A
5 V power input voltage	4.3	5.0	5.5	V
5 V power output voltage	2.5	-	5.5	V
5 V power input current	-	-	2.5	A
Serial I/F voltage	1.7	1.8	1.95	V
Operating ambient temperature	-10	-	85	°C
Operating junction temperature	-10	-	125	°C
P3 input voltage	-0.3	3.3	3.6	V
P3FW input voltage	-0.3	-	AVDD	V

## 7 Electrical characteristics

**Table 28. Device bias**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
I <sub>bias</sub>	-	E-fuses ON, regulators OFF	-	0.4	1.0	mA
I <sub>bias</sub>	-	E-fuses OFF, regulators ON (not switching) through V5out	-	-	1.0	mA

**Table 29. AVDD**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Output voltage	-	-	-	1.8	-	V
PORn rising	-	-	-	1.7	-	V
PORn falling	-	-	-	1.6	-	V
External capacitor	-	-	0.5	1	1.5	μF

**Table 30. P3 power disable**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
P3 low input voltage	-	Power enabled	-500	-	700	mV
P3 high input voltage	-	Power disabled	2.1	-	3.6	V
P3 pull-down resistor	-	R pull-down	60	100	140	kΩ
P3 input rising threshold	-	Rising	1.3	1.6	1.9	V
P3 input threshold hysteresis	-	Falling hysteresis	200	350	500	mV
P3FW low input voltage	-	P3 = w/NoFW enable	-500	-	700	mV
P3FW high input voltage	-	P3 = w/FW enable	1.0	-	AVDD	V
P3FW high input current	-	P3FW pin input current	-	-	5.0	μA

### 7.1 E-fuse 12 V

**Table 31. E-fuse 12 V**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On resistance	R <sub>dson</sub>	T <sub>j</sub> = 25 °C	-	45	-	mΩ
		T <sub>j</sub> = 125 °C	-	-	70	mΩ
Off state leakage current	I <sub>off</sub>	-	-	-	1	μA
Continuous output current	I <sub>out</sub>	-	-	2.5	-	A
Output clamp voltage	V <sub>oclamp</sub>	-	13.8	15	16.2	V
Input undervoltage lockout	V12uv	Falling	8.8	9.0	9.24	V
Undervoltage lockout hysteresis	-	R <sub>sing</sub> hysteresis	600	700	800	mV

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Current monitor output current gain	-	I <sub>mon</sub> /I <sub>E-fuse</sub> , I <sub>monG</sub> = 0 I <sub>out</sub> >= 200 mA	237.5	250	262.5	μA/A
	-	I <sub>mon</sub> /I <sub>E-fuse</sub> , I <sub>monG</sub> = 0 100 mA < I <sub>out</sub> < 200 mA	228	250	272	μA/A
	-	I <sub>mon</sub> /I <sub>E-fuse</sub> , I <sub>monG</sub> = 1	475	500	525	μA/A
Current monitor voltage	V <sub>I12sns</sub>	Max. voltage with unaffected precision	-	-	V <sub>I12out</sub> -1.5 V	V
Startup current limit	-	Until V <sub>I2out</sub> reaches its final value (either V <sub>I2in</sub> or the output clamp voltage limit)	0.5	0.8	1.1	A
Short-circuit current limit	-	V <sub>I2out</sub> < 7.5 V	0.5	0.8	1.1	A
Overload current limit	-	V <sub>I2out</sub> > 7.5 V (see Section 3.1.1 E-fuse 12 V current limit)	3	3.5	4	A

## 7.2 E-fuse 5 V

**Table 32. E-fuse 5 V**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Operating output voltage range	-	-	2.5	-	5.5	V
On resistance	R <sub>dson</sub>	T <sub>j</sub> = 25 °C	-	45	-	mΩ
		T <sub>j</sub> = 125 °C	-	-	70	mΩ
Off state leakage current	I <sub>off</sub>	-	-	-	1	μA
Continuous output current	I <sub>out</sub>	-	-	2.5	-	A
Output clamp voltage	V <sub>oclamp</sub>	-	5.70	6.00	6.30	V
Input undervoltage lockout rising	V <sub>on</sub>	E-fuse turn on voltage	4.25	4.35	4.45	V
Input undervoltage lockout falling	V <sub>off</sub>	E-fuse turn off voltage.	4.00	4.10	4.20	V
Output undervoltage comparator	V <sub>oth</sub>	Threshold to inform companion chip about power loss via EF5ON	-	4.4	-	V
EF5ON falling delay	-	Both V <sub>5in</sub> and V <sub>5out</sub> UV	-	-	500	ns
Current monitor output current gain	-	I <sub>mon</sub> /I <sub>E-fuse</sub> , I <sub>monG</sub> = 0 I <sub>uot</sub> >= 200 mA	237.5	250	262.5	μA/A
	-	I <sub>mon</sub> /I <sub>E-fuse</sub> , I <sub>monG</sub> = 0 100 mA < I <sub>uot</sub> < 200 mA	228	250	272	μA/A
	-	I <sub>mon</sub> /I <sub>E-fuse</sub> , I <sub>monG</sub> = 1	475	500	525	μA/A
Current monitor voltage	V <sub>I5sns</sub>	Max. voltage with unaffected precision	0	-	V <sub>5out</sub> -1.5 V	V
Reverse current voltage E-fuse off	V <sub>in-Vout</sub>	Possible to program via OTP as follows: -30 mV, -40 mV, -60 mV and -90 mV	-	-40	-	mV
Reverse current voltage E-fuse on	-	V <sub>in-Vout</sub>	-	0	-	mV
Startup current limit	-	Until V <sub>5out</sub> reaches its final value (either V <sub>5in</sub> or the output clamp voltage limit)	0.5	0.8	1.1	A
Short-circuit current limit	-	V <sub>5out</sub> < 2.5 V	0.5	0.8	1.1	A
Overload current limit	-	V <sub>5out</sub> > 2.5 V (see Section 3.2.1 E-fuse 5 V current limit)	3	3.5	4	A
EF5on Logic0 output voltage	-	I <sub>sink</sub> = 1 mA	-300	-	400	mV
I <sub>ol</sub> - EF5on	-	V <sub>ol</sub> = 0.4 V	-	11	-	mA
EF5on max. output voltage	-	-	-	-	V <sub>5outB</sub>	V

**7.3 VR33**
**Table 33. VR33**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Operating input voltage range	-	-	2.5	-	5.5	V
High-side FET on resistance	HSrdson	-	-	275	-	mΩ
		At 125 °C, 5 Vout = 5 V, Io = 500 mA	-	350	-	mΩ
		At 125 °C, 5 Vout = 3 V, Io = 500 mA	-	500	-	mΩ
Low-side FET on resistance	LSrdson	-	-	425	-	mΩ
		At 125 °C, 5 Vout = 5 V, Io = 500 mA	-	640	-	mΩ
		At 125 °C, 5 Vout = 3 V, Io = 500 mA	-	900	-	mΩ
DC output current	-	-	0	-	300	mA
Peak inductor overcurrent cycle-by-cycle limit	Ipeak_max	-	0.75	1	1.25	A
DC output voltage	-	Code 00000	-	2540	-	mV
	-	Code 10000	-	3180	-	mV
	-	Code 11111	-	3780	-	mV
Output voltage accuracy	-	-	-	±1	±3	%
DC output voltage step size	-	-	-	40	-	mV
VR33FB voltage range	-	-	-	-	V5outB	V
Vout5B voltage to enable startup	-	E-fuse 5 output voltage.	-	4.0	-	V
Soft-start slew rate	SR	-	5	6.25	7.5	V/ms
PG33 active voltage (falling)	-	PG level as function of output voltage setting	-9	-10	-11	%
PG33 deglitch filter	-	Deglitch = 0	-	200	-	ns
	-	Deglitch = 1	-	1	-	μs
PG33 Logic0 active output voltage	-	Isink = 1 mA	-300	-	400	mV
PG33 Logic1 in active output voltage delay	-	PG33 output high delay from PG33 comparator output being good.	-	1	-	ms
Total voltage output delta	-	200 mA step in 100 ns. Including DC.	-5	-	5	%
Switching frequency	-	-	-	-	6	MHz
Efficiency	-	At all operating conditions: V5out = 5.5 to 3 V, Iout = 150 mA, Rind = attempt (25 Ω at RT) , Rpcb = attempt (10 mΩ at RT)	80	90	-	%
VR has 100% duty capability.	-	-	-	-	-	-
Output capacitor	Co_vr33	All drift included	8.9	22	26.4	μF
Output capacitor ESR	Esr_vr33	At 4 MHz	1	-	30	mΩ
Output inductor	Lo_vr33	All drift included	0.56	1	1.2	μH
Output inductor resistance	Rind_vr33	-	-	-	100	mΩ

**7.4 VR09**
**Table 34. VR09**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Operating input voltage range	-	-	2.5	-	5.5	V
High-side FET on resistance	HSrdson	-	-	75	-	mΩ
		At 125 °C, Vgs = 5 V, Io = 500 mA	-	90	-	mΩ
		At 125 °C, Vgs = 3 V, Io = 500 mA	-	135	-	mΩ
Low-side FET on resistance	LSrdson	-	-	20	-	mΩ
		At 125 °C, Vgs = 5 V, Io = 500 mA	-	30	-	mΩ
		At 125 °C, Vgs = 3 V, Io = 500 mA	-	40	-	mΩ
DC/RMS output current	-	-	0	-	3.50	A
Pulse output current	-	Tpulse 500 μs	-	-	4.30	A
Peak inductor overcurrent cycle-by-cycle limit	Ipeak_max	-	6.4	7.1	7.8	A
Overcurrent Toff time	-	-	-	-	800	ns
DC output voltage	-	Code 000000	-	770	-	mV
	-	Code 100000	-	930	-	mV
	-	Code 111111	-	1085	-	mV
Output voltage accuracy	-	-	-	±1	±3	%
DC output voltage step size	-	-	-	5	-	mV
VR09En input voltage for VR09 turn-on	-	VR09 turn on voltage	1.0	-	3.65	V
VR09En input voltage for VR09 turn-off	-	VR09 turn off voltage	-0.3	-	0.4	V
VR09En input voltage hysteresis for VR09 turn off.	-	VR09 turn-off hysteresis	100	200	-	mV
VR09En input bias	-	-	-	-	1	μA
Soft-start slew rate	SR	-	1	1.5	2	V/ms
PG09 activation voltage	-	PG voltage as percentage of output voltage setting	-9	-10	-11	%
PG09 deglitch filter	-	Deglitch = 0	-	200	-	ns
		Deglitch = 1	-	1	-	μs
PG09 Logic0 active output voltage	-	Isink = 1 mA	-300	-	400	mV
PG09 Logic1 in active output voltage delay	-	PG09 output high delay from PG09 comparator output being good.	-	1	-	ms
Total output voltage delta	-	1A75 step in 100 ns	-5	-	5	%
Switching frequency	-	-	-	2	-	MHz
Efficiency	-	V5out = 5, Iout = 1A5, Rind = attempt (25 Ω at RT), Rpcb = attempt (10 Ω at RT)	-	79	-	%
Output capacitor	Co_vr09	All drift included 2 x 47 μF in //	28	44	113	μF
Output capacitor ESR	Esr_vr09	At 2 MHz for each of the 47 μF cap	1	-	20	mΩ
Output inductor	Lo_vr09	All drift included	0.26	0.47	0.57	μH
Output inductor resistance	Rind_vr09	-	-	30	50	mΩ

## 7.5 Temperature monitor

**Table 35. Temperature monitor**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Early overtemperature warning	EOTW	-	130	145	160	°C
Overtemperature threshold	OTth	-	150	165	180	°C
Overtemperature hysteresis	OTHys	-	-	50	-	°C
Temperature warning to shutdown tracking	Tdelta	OTth- EOTW	15	20	25	°C

## 7.6 I<sup>2</sup>C bus

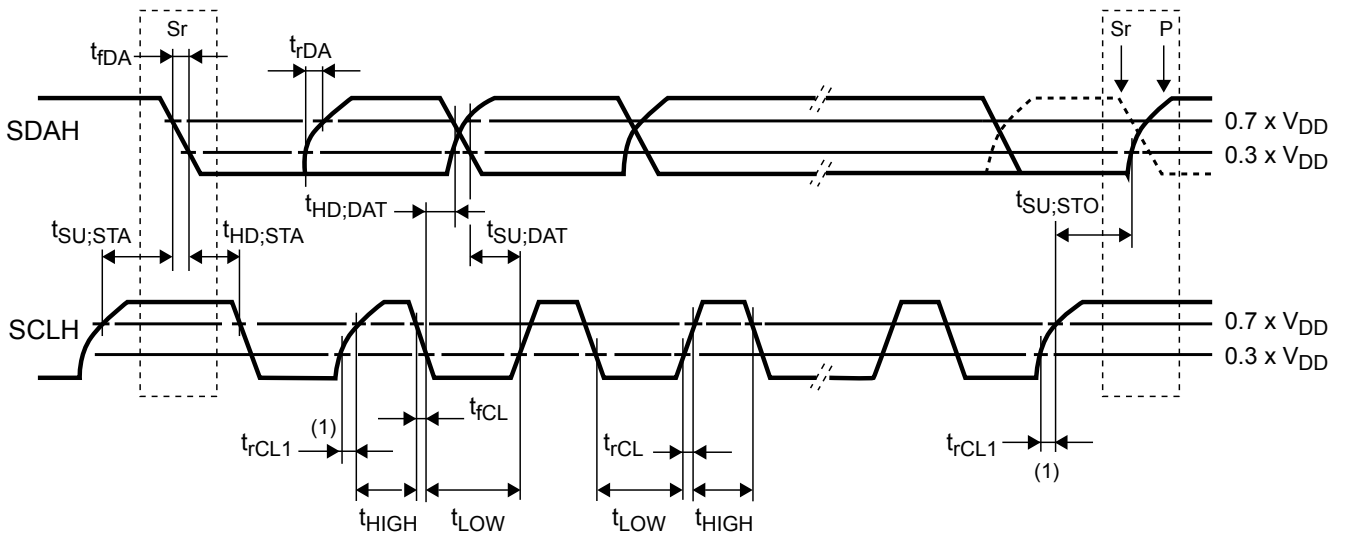
The I<sup>2</sup>C signals must be compliant to the standard I<sup>2</sup>C bus characteristics, the device is compatible with the mode "Normal", "Fast", "Fast Plus" and "High Speed".

**Table 36. I<sup>2</sup>C**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Vol-SINTn	-	Vol = 7 mA	-	-	0.4	V
Iol-SINTn	-	Vol = 0v4	7	12	-	mA
VDD for I <sup>2</sup> C interface	-	-	1.7	1.8	1.95	V
Vil	-	Logic0 input voltage	-0.5	-	0.3 VDD	V
Vih	-	Logic1 input voltage	0.7 VDD	-	VDD +0.5	V
Vihyst	-	Input hysteresis	0.1 VDD	-	-	V
Iin	-	Input current, Vi = 0.1 VDD to 0.9 V	-10	-	10	µA
Vol-SDA	-	Logic0 output voltage, Isink = 2 mA	0	-	0.2 VDD	V
Iol-SDA	-	Vol = 0.4 V	6	8	-	mA
Ron-SDA	-	Vol = 0.4 V	-	50	-	Ω
Input voltage deglitch	-	-	0	-	10	ns
SCL clock frequency	-	-	0.1	-	3.4	MHz
tsu, start/stop	-	Setup time	160	-	-	ns
thold, start/stop	-	Hold time	160	-	-	ns
tlow, SCL	-	Low pulse time	160	-	-	ns
thi, SCL	-	High pulse time	60	-	-	ns
tsu, SDA	-	Data setup time	10	-	-	ns
thold, SDA	-	Data hold time	0	-	70	ns
trise, tfall, SCL receiver	-	Clock rise/fall time	20	-	1000	ns
trise, tfall, SDA receiver	-	Data rise/fall time	20	-	1000	ns
tfall, SDA transmitter	-	(1)	20	-	40	ns

1. This need to be achieved with the help of the pull-up resistor (and if needed extra cap) taking in consideration the board and the load (C and R) connected to the SDA pin.

Figure 19. I<sup>2</sup>C bus diagram



= MCS current source pull-up

= Rp resistor pull-up

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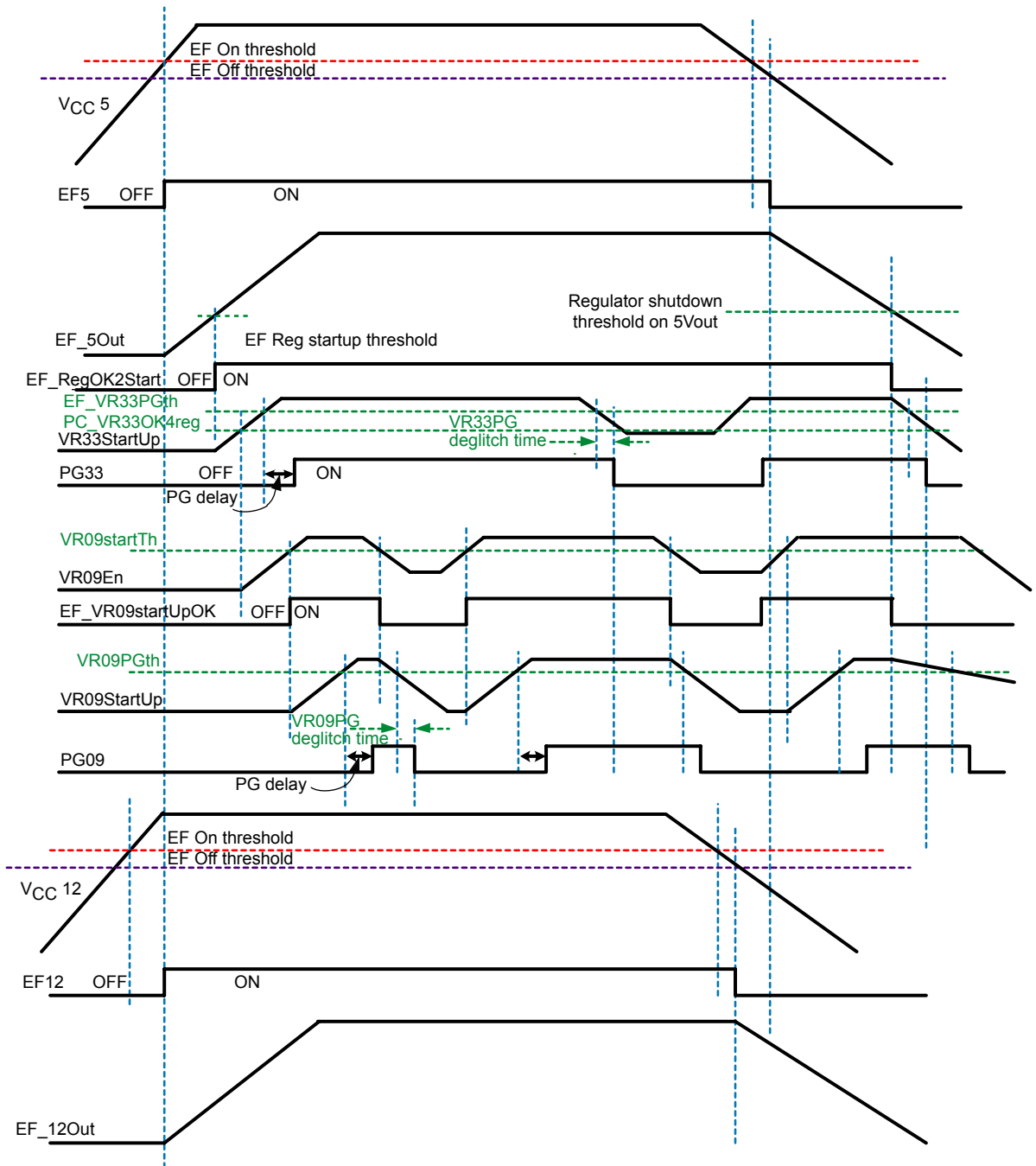
1. First rising edge of the SCLH signal after Sr and after each acknowledge bit.



## 8 Application details

### 8.1 Regulators sequencing

Figure 20. Regulators sequencing



A typical power-on sequence for the system is as follows:

1. The V5IN and/or V12IN goes above the required operating voltage to start the STPMIC02.
2. If the V5IN is above the UV5 threshold, the E-fuse 5 V starts ramping its output.
3. If the V12IN is above the UV12 threshold, the E-fuse 12 V starts ramping its output. Since the E-fuses are independent from each other, it can happen that both E-fuse 5 V and E-fuse 12 V are ramping up at the same time.
4. Upon the V5OUTB crossing the regulator minimum operating voltage for turn ON, the VR33 starts up.
5. After the VR33 output crosses its PG detection threshold, the PG33 signal goes to Logic1 1 ms after the last time that the VR33 is above its target have stabilized.
6. The VR09 starts up after the VR09EN pin is at the Logic1 state.
7. After the VR09 output crosses its PG detection threshold, the PG09 signal goes to Logic1 1 ms after the last time that VR09 is above its target have stabilized.
8. If the V5IN or V12IN input fails, its respective E-fuse 5 V / E-fuse 12 V is open.
9. If both V5IN and V12IN inputs fail, both E-fuse 5 V / E-fuse 12 V are open and the STPMIC02 continues operating from the V5OUTB.

## 8.2 Disabling VR33

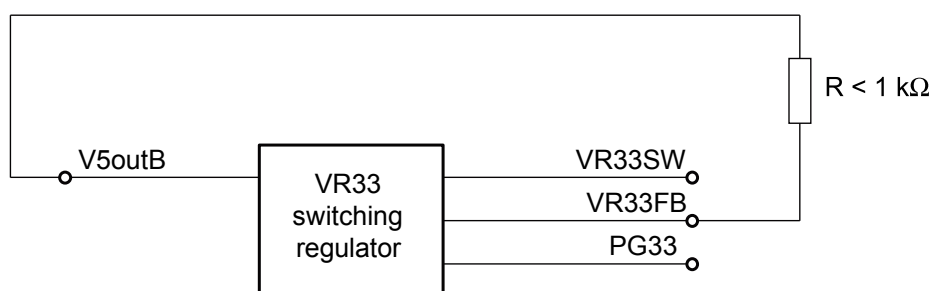
The VR33 is an always-on regulator. As soon as the V5OUTB is present and above the UV threshold, the VR33 is enabled. The VR33 does not have a corresponding bit in the register map that would allow to switch off (disable) the regulator.

In case the VR33 is not used in an application, it has to be configured in such a way that prevents the VR33 from switching in order to save switching losses and to have the regulator in a defined state. In particular, the user has to:

- Pull the VR33FB pin to the V5OUTB with resistance lower than 1 kΩ (can also be a short).
- Force the VR33PWM bit in the CONTROL0 register to Logic1 before enabling the VR09.

In this state, the STPMIC02 internal low-side power device of the VR33 is turned on, pulling the VR33SW node to ground. Since the state of the VR33SW pin is defined by the STPMIC02 itself in this configuration, there is no need to populate the L and C components related to the VR33 on the PCB.

**Figure 21. Hardware 3.3 V regulator disable**



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**Table 37. Fault function**

Signals (which are latched)								
Type of fault	PG09	PG33	SINTn pin	E-fuse 5 V	E-fuse 12 V	0.94 V regulator	3.3 V regulator	Status set
Vin12 undervoltage	H	H	H ⇒ L	-	Open	Enable	Enable	UV12
V5in undervoltage	H	H	H ⇒ L	Open	-	Enable	Enable	UV5

Signals (which are latched)								
Type of fault	PG09	PG33	SINTn pin	E-fuse 5 V	E-fuse 12 V	0.94 V regulator	3.3 V regulator	Status set
Vout12 overcurrent <sup>(1)</sup>	H	H	H ⇒ L	Closed	Enable (Iout12 limit)	Enable	Enable	OC12
Vout5 overcurrent <sup>(1)</sup>	H	H	H ⇒ L	Enable (Iout5 limit)	Closed	Enable	Enable	OC5
0.9 V reg. output UV (-10%)	H ⇒ L	H	H ⇒ L	Closed	Closed	Enable (recovery)	Enable	UV09
3.3 V reg. output UV (-10%)	H	H ⇒ L	H ⇒ L	Closed	Closed	Enable	Enable (recovery)	UV33
0.9 V overcurrent	H	H	H ⇒ L	Closed	Closed	Enable (Iout limit)	Enable	OC09
3.3 V overcurrent	H	H	H ⇒ L	Closed	Closed	Enable	Enable (Iout limit)	OC33
12 V early overtemp. warning	H	H	H ⇒ L	Closed	Closed	Enable	Enable	EOTW12
5 V early overtemp. warning	H	H	H ⇒ L	Closed	Closed	Enable	Enable	EOTW5
0.9 V early overtemp. warning	H	H	H ⇒ L	Closed	Closed	Enable	Enable	EOTW09
5 V overtemperature	H	H	H ⇒ L	Open	Closed	Enable	Enable	OT5
12 V overtemperature	H	H	H ⇒ L	Closed	Open	Enable	Enable	OT12
0.9 V overtemperature	H	H	H ⇒ L	Closed	Closed	Enable	Enable	OT5 and 12
V5outB UV 2.5 V for regulator operation (cannot maintain regulator performance)	L	L	H	-	-	Disable	Disable	-
P3 pin Logic1 (feature enabled)	-	-	H ⇒ L	Open	Open	-	-	P3state match pin

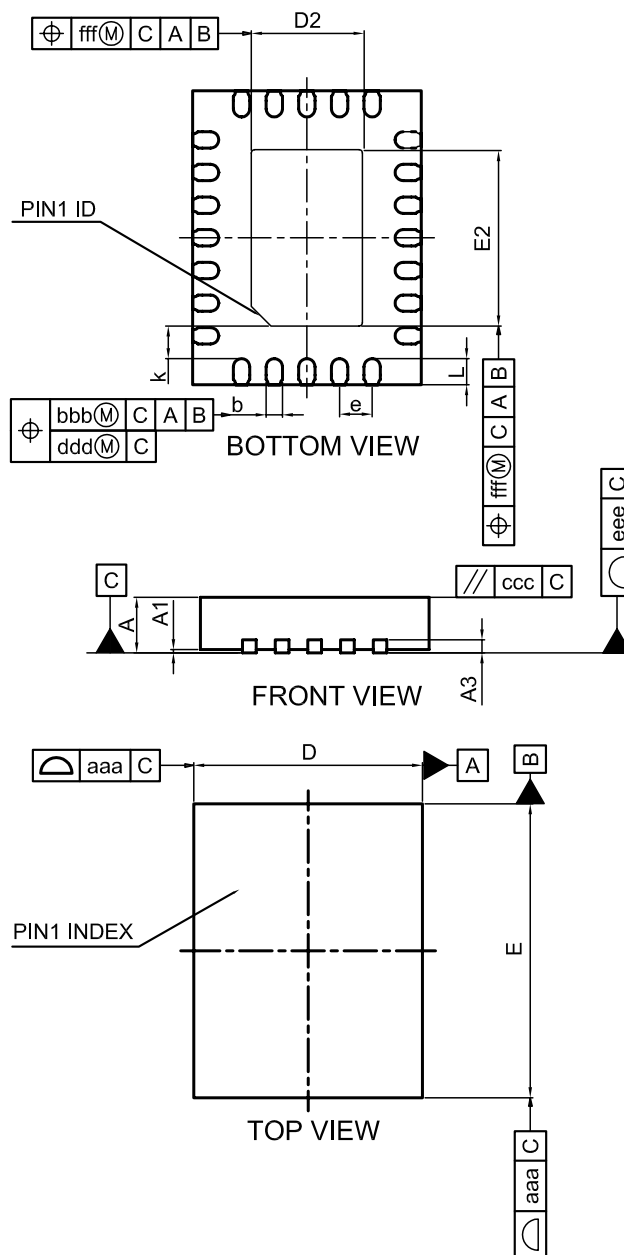
1. An overcurrent during the start-up is not a fault, it signals ramp-up in progress, the load should be less than the startup current limit.

## 9 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK<sup>®</sup>** packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 9.1 VQFN 24-pin 3.5 x 4.5 x 1.0 mm, 0.5 mm pitch with EPAD package information

Figure 22. VQFN 24-pin 3.5 x 4.5 x 1.0 mm, 0.5 mm pitch with EPAD package outline



**Table 38. VQFN 24-pin 3.5 x 4.5 x 1.0 mm, 0.5 mm pitch with EPAD package dimensions**

Symbol	Dimensions		
	Min.	Nom.	Max.
A	0.80	0.85	0.90
A1	-	-	0.05
b	0.20	0.25	0.30
D	3.40	3.50	3.60
D2	1.60	1.70	1.80
E	4.40	4.50	4.60
E2	2.60	2.70	2.80
e	0.50 BSC		
L	0.30	0.40	0.50
k	0.30	-	-
N	24		
<b>Tolerance of form and position</b>			
aaa	0.15		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		
fff	0.10		

## 10 Recommended external components

**Table 39. Recommended external components**

From	To	Description	Value	Unit
VR09FB	GND	Output capacitor	2 x 47 or 2 x 22 or 1 x 47	μF
VR09SW	VR09FB	Inductor	0.47	μH
VR33FB	GND	Output capacitor	22	μF
VR33SW	VR33FB	Inductor	1	μH
AVDD	GND	Capacitor	1	μF
System supply	V5in	Lead inductance	<1	μH
V5in	GND	Capacitor	1	μF
V5out	GND	Capacitor	>10 (STPMIC02) >47 or >2 x 22 (application)	μF
System supply	V12in	Lead inductance	<1	μH
V12in	GND	Capacitor	1	μF
V12out	GND	Capacitor	>10	μF

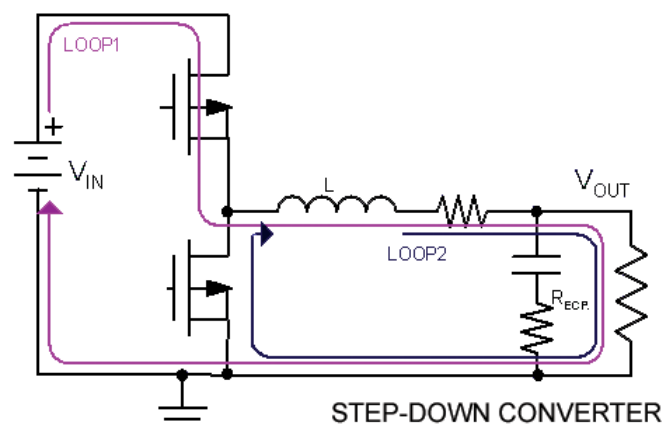
## 11 PCB design rules guideline

### 11.1 Basic principles

A step-down converter reduces an incoming voltage to a lower output voltage. A switching element, typically a bipolar or a MOSFET is switched on and off. When the switch is on, the input supply charges the inductor and capacitor and delivers power to the load. During this time, the magnitude of the inductor current ramps up as it flows through the Loop 1.

When the MOSFET turns off, the input is disconnected from the output, and the inductor and output capacitor support the load. The magnitude of the inductor current ramps down as it flows through the recirculating element, following the direction indicated in the Loop 2. The recirculating element can be a diode, but recently a more efficient synchronous rectification system is used where a second switching element takes over the function of the diode.

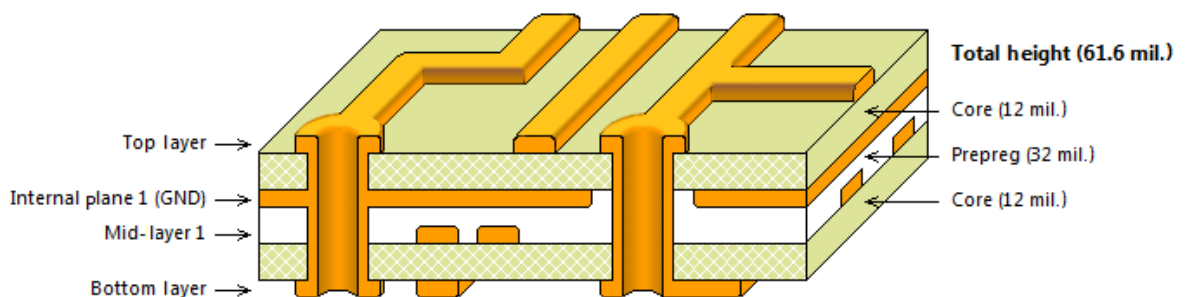
Figure 23. Current loops



### 11.2 Layout rules

A multilayer board is preferred using the top layer to contain all power routing for the devices, and the inner layer 1 as a ground return plane.

Figure 24. Layer stack



#### 11.2.1 Supplies

An incoming supply per switcher should be adequately buffered using an input capacitor. Refer to the device specification for suggested values. This capacitor needs to be placed as close as possible to the  $V_{IN}$  pin to minimize the loop area.

**11.2.2 Switch node**

The switch node is the pin feeding the inductor. Keep the switch node as short as possible to avoid power losses. Do not make it wider than necessary to avoid capacitive loading of the switch node.

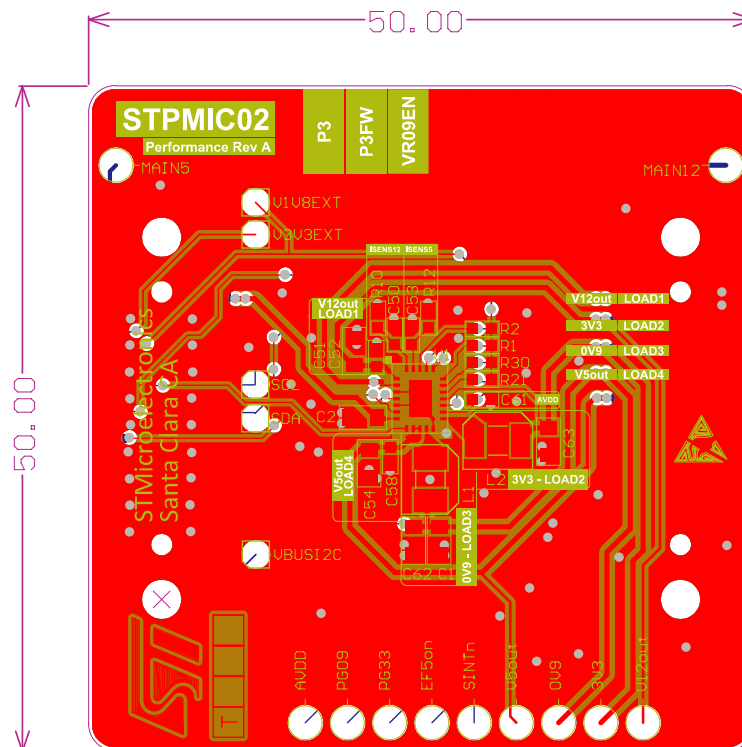
**11.2.3 Feedback node**

The feedback node is a high impedance input and thus sensitive to noise and current injection through the capacitive and magnetic coupling. Keep the feedback lines away from large switching surfaces or magnetic fields. Remember that magnetic fields are not stopped by copper!

Feedback components should be connected to a clean return pathway and never share return paths with the main switching elements.

**11.2.4 Output capacitors**

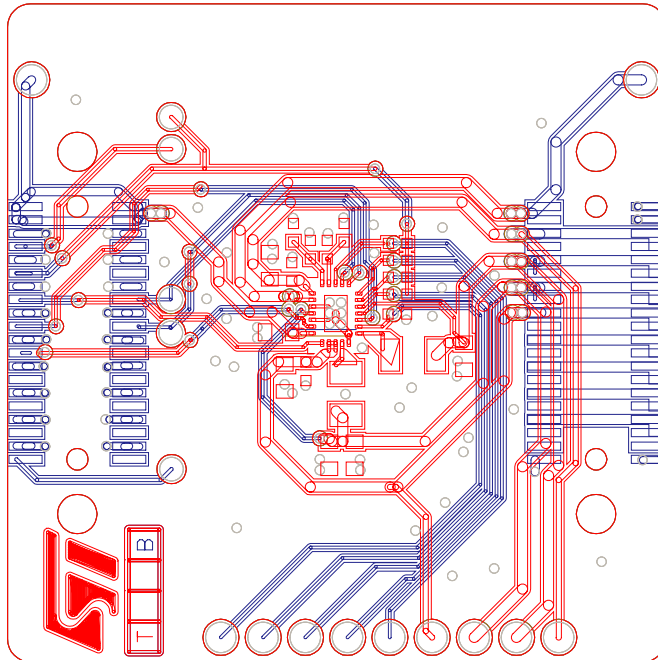
Multiple output capacitors are preferred over a single one. Each capacitor should have its own return via.

**11.2.5 PCB layout recommendation**
**Figure 25. All layers**


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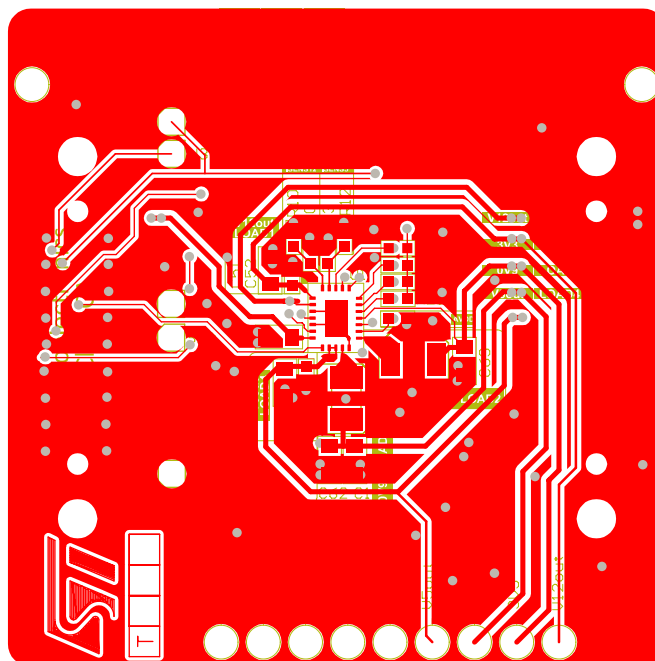


Figure 26. All layers (through view)



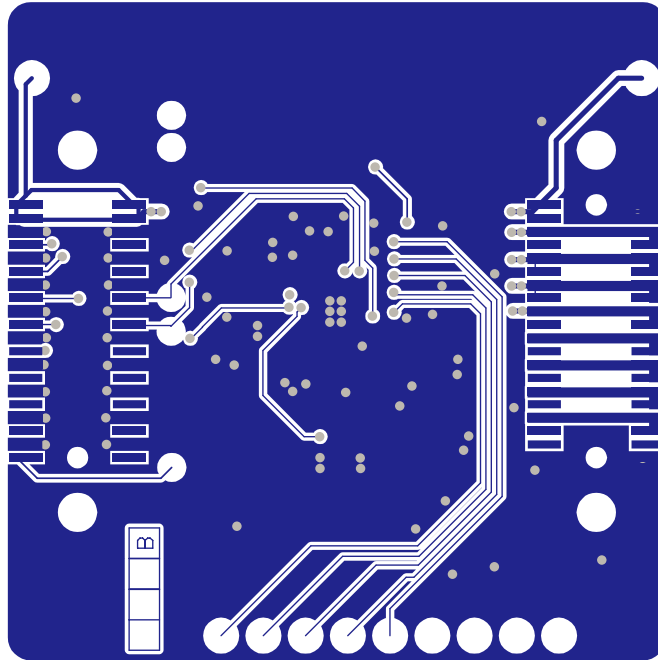
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Figure 27. Top layer



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Figure 28. Bottom layer



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### 11.3 General rules

- Do not share vias. Every component connecting to the power or reference plane needs its own via. For large currents multiple vias are to be preferred.
- Vias shall be placed as close to the component pin as possible.
- Feedback nodes are sensitive. Keep them away from magnetic fields and nodes that may capacitive couple energy into them.

### 11.4 Thermal aspects

The device package uses the center pad as a thermal conduit. This pad should be connected to an adequate spread of copper. When following the suggested layer stack the internal ground plane may be sufficient. If lots of other heat generating components are close by it may be necessary to create an exposed copper area on the backside of the board. The pad should be connected using multiple vias.

## **12 Evaluation tool**

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An evaluation tool is available upon request. Please contact your local ST sales representative for availability.

## Revision history

**Table 40. Document revision history**

Date	Revision	Changes
22-Dec-2015	1	Initial release.
01-Feb-2016	2	Updated document status to not found. Minor modifications throughout document.
03-Mar-2016	3	Updated <a href="#">Section 3.9 I2C serial interface</a> (added <a href="#">Section 3.9.1 Slave address</a> and <a href="#">Section 3.9.2 I2C functional operation</a> ). Minor modifications throughout document.
17-Jan-2019	4	Added thermal resistance to <a href="#">Table 26. Absolute maximum ratings</a> ; Updated <a href="#">Table 38. VQFN 24-pin 3.5 x 4.5 x 1.0 mm, 0.5 mm pitch with EPAD package dimensions</a> .

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